EMC 性能优异的 ISO776x 高速、增强型六通道数字隔离器

1 特性

- 100Mbps 数据速率
- 稳健可靠的隔离栅：
  - 预计寿命超过 30 年
  - 隔离等级高达 5000V_{RMS}
  - 浪涌能力高达 12.8 kV
  - CMTI 典型值为 ±100kV/μs
- 宽电源电压范围：2.25V 至 5.5V
- 2.25V 至 5.5V 电平转换
- 默认输出*高电平* (ISO776x) 和*低电平* (ISO776xF) 选项
- 宽温度范围：–55°C 至 +125°C
- 低功耗，1Mbps 时每通道的电流典型值为 1.4mA
- 低传播延迟：5V 时为 11ns（典型值）
- 优异的电磁兼容性 (EMC)：
  - 系统级 ESD、EFT 和浪涌抗扰性
  - 在整个隔离栅具有 ±8kV IEC 61000-4-2 接触放电保护
  - 低辐射
- 宽体 SOIC (DW-16) 和 SSOP (DBQ-16) 封装选项
- 提供汽车版本：*ISO776x-Q1*
- 安全相关认证：
  - 符合 DIN EN IEC 60747-17 (VDE 0884-17) 标准的增强型绝缘
  - UL 1577 组件认证计划
  - 符合 IEC 62368-1 和 IEC 60601-1 标准的 CSA 认证
  - 符合 GB4943.1 标准的 CQC 认证
  - 符合 EN 62368-1 和 EN 61010-1 标准的 TUV 认证

2 应用

- 工业自动化
- 电机控制
- 电源
- 光伏逆变器
- 医疗设备

3 说明

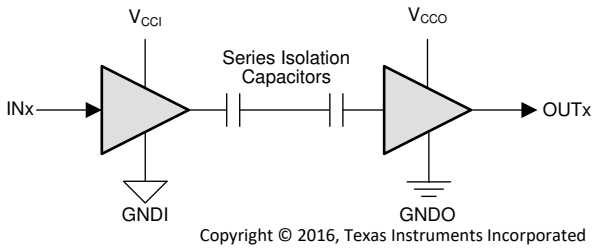
ISO776x 器件是高性能六通道数字隔离器，可提供符合 UL 1577 的 5000V_{RMS}（DW 封装）和 3000V_{RMS}（DBQ 封装）隔离额定值。该系列器件还通过了 VDE、CSA、TUV 和 CQC 认证。

在隔离 CMOS 或 LVCMOS 数字 I/O 的同时，ISO776x 系列的器件还可提供高电磁抗扰度和低辐射，同时具备低功耗特性。每个隔离通道都有一个由二氧化硅 (SiO_2) 绝缘栅分开的逻辑输入和逻辑输出缓冲器。ISO776x 系列的器件采用所有可能的引脚配置，因此所有六个通道都可以处于同一方向，或者一个、两个或三个通道处于反向，而其余通道处于正向。如果输入电源或信号丢失，不带后缀 F 的器件默认输出*高电平*，带后缀 F 的器件默认输出*低电平*。更多详细信息，请参阅*器件功能模式*部分。

该系列器件与隔离式电源结合使用，有助于防止数据总线（例如，RS-485、RS-232 和 CAN）或者其他电路上的噪声电流进入本地接地以及干扰或损坏敏感电路。凭借创新型芯片设计和布局技术，ISO776x 系列器件的电磁兼容性得到了显著增强，可缓解系统级 ESD、EFT 和浪涌问题并符合辐射标准。ISO776x 系列器件可采用 16 引脚 SOIC 和 SSOP 封装。

器件信息

器件型号	封装	封装尺寸（标称值）
ISO7760 ISO7761 ISO7762 ISO7763	SOIC (16)	10.30mm × 7.50mm
	SSOP (16)	4.90mm × 3.90mm



V_{CCI}=输入 V_{CC}，V_{CCO}=输出 V_{CC}
GNDI=输入接地，GNDO=输出接地

简化版原理图

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4 Pin Configuration and Functions

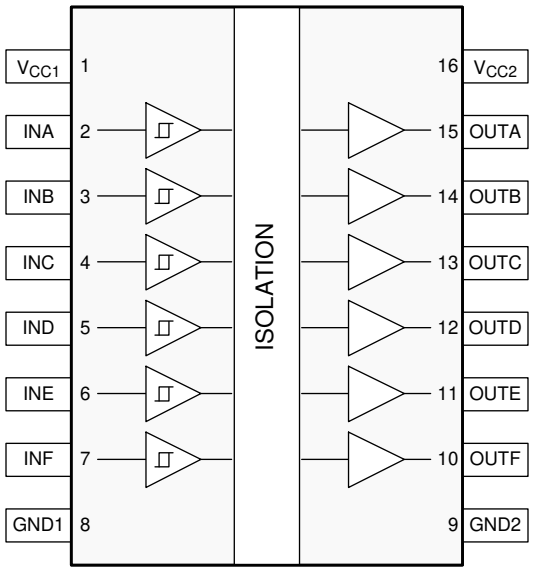


图 4-1. ISO7760 DW and DBQ Packages 16-Pin SOIC and SSOP Top View

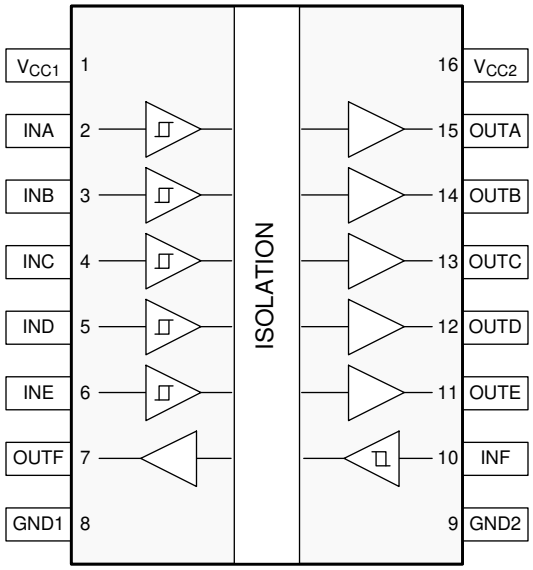


图 4-2. ISO7761 DW and DBQ Packages 16-Pin SOIC and SSOP Top View

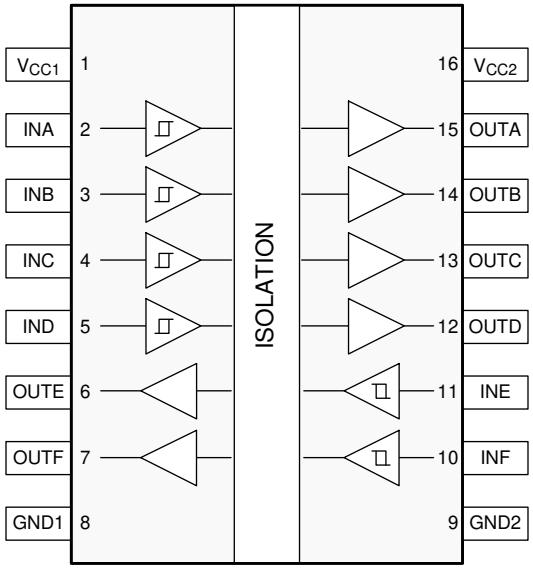


图 4-3. ISO7762 DW and DBQ Packages 16-Pin SOIC and SSOP Top View

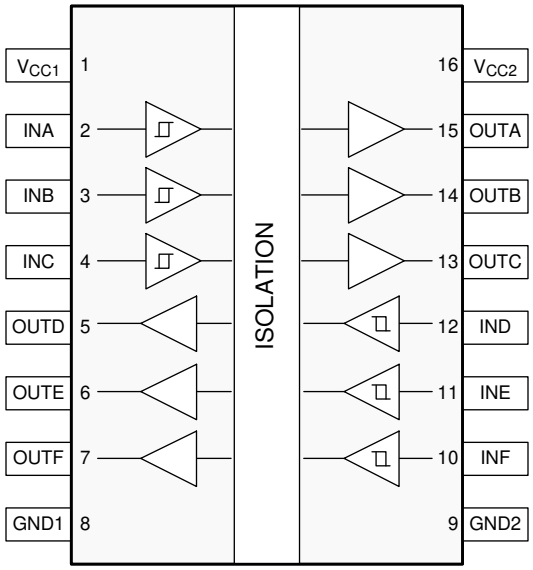


图 4-4. ISO7763 DW and DBQ Packages 16-Pin SOIC and SSOP Top View

表 4-1. Pin Functions

PIN					I/O	DESCRIPTION
NAME	NO.					
	ISO7760	ISO7761	ISO7762	ISO7763		
GND1	8	8	8	8	—	Ground connection for V_{CC1}
GND2	9	9	9	9	—	Ground connection for V_{CC2}
INA	2	2	2	2	I	Input, channel A
INB	3	3	3	3	I	Input, channel B
INC	4	4	4	4	I	Input, channel C
IND	5	5	5	12	I	Input, channel D
INE	6	6	11	11	I	Input, channel E
INF	7	10	10	10	I	Input, channel F
OUTA	15	15	15	15	O	Output, channel A
OUTB	14	14	14	14	O	Output, channel B
OUTC	13	13	13	13	O	Output, channel C
OUTD	12	12	12	5	O	Output, channel D
OUTE	11	11	6	6	O	Output, channel E
OUTF	10	7	7	7	O	Output, channel F
V_{CC1}	1	1	1	1	—	Power supply, side 1
V_{CC2}	16	16	16	16	—	Power supply, side 2

5 Specifications

5.1 Absolute Maximum Ratings

See(1)

		MIN	MAX	UNIT
V_{CC1}, V_{CC2}	Supply voltage (2)	-0.5	6	V
V	Voltage at INx, OUTx	-0.5	V_{CCX} + 0.5 (3)	V
I_o	Output current	-15	15	mA
T_J	Junction temperature		150	°C
T_{stg}	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values
(3) Maximum voltage must not exceed 6 V.

5.2 ESD Ratings

(1) (2)

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM),per ANSI/ESDA/JEDEC JS-001, all pins (1)	±6000	V
		Charged device model (CDM),per JEDEC specification JESD22-C101, all pins(2)	±1500	
		Contact discharge per IEC 61000-4-2; Isolation barrier withstand test(3) (4)	±8000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.
(3) IEC ESD strike is applied across the barrier with all pins on each side tied together creating a two-terminal device.
(4) Testing is carried out in air or oil to determine the intrinsic contact discharge capability of the device.

5.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V_{CC1}, V_{CC2}	Supply Voltage		2.25		5.5	V
$V_{cc\ (UVLO+)}$	UVLO threshold when supply voltage is rising			2	2.25	V
$V_{cc\ (UVLO-)}$	UVLO threshold when supply voltage is falling		1.7	1.8		V
$V_{HYS\ (UVLO)}$	Supply voltage UVLO hysteresis		100	200		mV
I_{OH}	High level output current	V_{CCO} (1) = 5 V	-4			mA
		V_{CCO} = 3.3 V	-2			
		V_{CCO} = 2.5 V	-1			
I_{OL}	Low level output current	V_{CCO} = 5 V			4	mA
		V_{CCO} = 3.3 V			2	
		V_{CCO} = 2.5 V			1	
V_{IH}	High level Input voltage		0.7 x V_{CCI} (1)		V_{CCI}	V
V_{IL}	Low level Input voltage		0		0.3 x V_{CCI}	V
DR(2)	Data Rate		0		100	Mbps
T_A	Ambient temperature		-55	25	125	°C

(1) V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}
(2) 100 Mbps is the maximum specified data rate, although higher data rates are possible.

5.4 Thermal Information

THERMAL METRIC (1)		ISO776x		UNIT
		DW (SOIC)	DBQ (SSOP)	
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	60.3	86.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	24.0	26.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	29.3	36.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	3.3	1.7	°C/W
ψ_{JB}	Junction-to-board characterization parameter	28.7	36.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO7760						
P_D	Maximum power dissipation (both sides)	V_{CC1} = V_{CC2} = 5.5 V, T_J = 150°C, C_L = 15 pF, Input a 50-MHz 50% duty cycle square wave			314	mW
P_{D1}	Maximum power dissipation (side-1)				55	mW
P_{D2}	Maximum power dissipation (side-2)				259	mW
ISO7761						
P_D	Maximum power dissipation (both sides)	V_{CC1} = V_{CC2} = 5.5 V, T_J = 150°C, C_L = 15 pF, Input a 50-MHz 50% duty cycle square wave			314	mW
P_{D1}	Maximum power dissipation (side-1)				88	mW
P_{D2}	Maximum power dissipation (side-2)				226	mW
ISO7762						
P_D	Maximum power dissipation (both sides)	V_{CC1} = V_{CC2} = 5.5 V, T_J = 150°C, C_L = 15 pF, Input a 50-MHz 50% duty cycle square wave			314	mW
P_{D1}	Maximum power dissipation (side-1)				122	mW
P_{D2}	Maximum power dissipation (side-2)				192	mW
ISO7763						
P_D	Maximum power dissipation (both sides)	V_{CC1} = V_{CC2} = 5.5 V, T_J = 150°C, C_L = 15 pF, Input a 50-MHz 50% duty cycle square wave			314	mW
P_{D1}	Maximum power dissipation (side-1)				157	mW
P_{D2}	Maximum power dissipation (side-2)				157	mW

5.6 Insulation Specifications

PARAMETER		TEST CONDITIONS		VALUE		UNIT
				DW-16	DBQ-16	
CLR	External clearance(1)	Shortest terminal-to-terminal distance through air		>8	>3.7	mm
CPG	External creepage(1)	Shortest terminal-to-terminal distance across the package surface		>8	>3.7	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)		>17	>17	µm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112; UL 746A		>600	>600	V
	Material group	According to IEC 60664-1		I	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 150 V_{RMS}		I-IV	I-IV	
		Rated mains voltage ≤ 300 V_{RMS}		I-IV	I-III	
		Rated mains voltage ≤ 600 V_{RMS}		I-IV	n/a	
		Rated mains voltage ≤ 1000 V_{RMS}		I-III	n/a	
DIN EN IEC 60747-17 (VDE 0884-17)(2)						
V_{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)		2121	566	V_{PK}
V_{IOWM}	Maximum working isolation voltage	AC voltage; Time dependent dielectric breakdown (TDDB) test; See 图 8-7		1500	400	V_{RMS}
		DC voltage		2121	566	V_{DC}
V_{IOTM}	Maximum transient isolation voltage	$V_{TEST} = V_{IOTM}$, t = 60 s (qualification); $V_{TEST} = 1.2 \times V_{IOTM}$, t= 1 s (100% production)	ISO7760	8000	4242	V_{PK}
			ISO7761, ISO7762, ISO7763	7071		
V_{IMP}	Maximum impulse voltage(3)	Tested in air, 1.2/50-µs waveform per IEC 62368-1		8000	4000	V_{PK}
V_{IOSM}	Maximum surge isolation voltage(4)	$V_{IOSM} \geq 1.3 \times V_{IMP}$; Tested in oil (qualification test), 1.2/50-µs waveform per IEC 62368-1		12800	10000	V_{PK}
q_{pd}	Apparent charge(5)	Method a, After Input-output safety test subgroup 2/3, $V_{ini} = V_{IOTM}$, t_{ini} = 60 s; $V_{pd(m)} = 1.2 \times V_{IORM}$, t_m = 10 s		≤5	≤5	pC
		Method a, After environmental tests subgroup 1, $V_{ini} = V_{IOTM}$, t_{ini} = 60 s; $V_{pd(m)} = 1.6 \times V_{IORM}$, t_m = 10 s		≤5	≤5	
		Method b: At routine test (100% production) and preconditioning (type test); $V_{ini} = 1.2 \times V_{IOTM}$, t_{ini} = 1 s; $V_{pd(m)} = 1.875 \times V_{IORM}$, t_m = 1 s (method b1) or $V_{pd(m)} = V_{ini}$, $t_m = t_{ini}$ (method b2)		≤5	≤5	
C_{IO}	Barrier capacitance, input to output(6)	V_{IO} = 0.4 x sin (2πft), f = 1 MHz		~1.1	~0.9	pF
R_{IO}	Isolation resistance(6)	V_{IO} = 500 V, T_A = 25°C		$>10^{12}$	$>10^{12}$	Ω
		V_{IO} = 500 V, 100°C ≤ T_A ≤ 125°C		$>10^{11}$	$>10^{11}$	
		V_{IO} = 500 V, T_S = 150°C		$>10^{9}$	$>10^{9}$	
	Pollution degree			2	2	
	Climatic category			55/125/21	55/125/21	
UL 1577						
V_{ISO}	Maximum withstanding isolation voltage	$V_{TEST} = V_{ISO}$, t = 60 s (qualification), $V_{TEST} = 1.2 \times V_{ISO}$, t = 1 s (100% production)		5000	3000	V_{RMS}

(1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed-circuit board are used to help increase these specifications.

(2) This coupler is suitable for *safe electrical insulation* only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
(3) Testing is carried out in air to determine the surge immunity of the package
(4) Testing is carried out in oil to determine the intrinsic surge immunity of the isolation barrier.
(5) Apparent charge is electrical discharge caused by a partial discharge (pd).
(6) All pins on each side of the barrier tied together creating a two-terminal device.

5.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV
Certified according to DIN EN IEC 60747-17 (VDE 0884-17)	Certified according to IEC 62368-1 and IEC 60601-1	Recognized under UL 1577 Component Recognition Program	Certified according to GB 4943.1	Certified according to EN 61010-1 and EN 62368-1
Reinforced Insulation; Maximum transient isolation voltage, 8000 V_{PK} (ISO7760 in DW-16), 7071 V_{PK} (ISO7761, ISO7762, ISO7763 in DW-16) and 4242 V_{PK} (DBQ-16); Maximum repetitive peak isolation voltage, 2121 V_{PK} (DW-16) and 566 V_{PK} (DBQ-16); Maximum surge isolation voltage, 12800 V_{PK} (DW-16) and 10000 V_{PK} (DBQ-16)	Reinforced insulation per CSA 62368-1 and IEC 62368-1 800 V_{RMS} (DW-16) and 370 V_{RMS} (DBQ-16) maximum working voltage (pollution degree 2, material group I); DW-16: 2 MOPP (Means of Patient Protection) per CSA 60601-1 and IEC 60601-1, 250 V_{RMS} maximum working voltage	DW-16: Single protection, 5000 V_{RMS} ; DBQ-16: Single protection, 3000 V_{RMS}	DW-16: Reinforced Insulation, Altitude ≤ 5000 m, Tropical Climate, 700 V_{RMS} maximum working voltage; DBQ-16: Basic Insulation, Altitude ≤ 5000 m, Tropical Climate, 400 V_{RMS} maximum working voltage	5000 V_{RMS} Reinforced insulation per EN 61010-1 up to working voltage of 600 V_{RMS} (DW-16) and 300 V_{RMS} (DBQ-16) 5000 V_{RMS} Reinforced insulation per EN 62368-1 up to working voltage of 600 V_{RMS} (DW-16) and 370 V_{RMS} (DBQ-16)
Certificate number: 40040142	Master contract number: 220991	File number: E181974	Certificate numbers: CQC15001121716 (DW) CQC18001199097 (DBQ)	Client ID number: 77311

5.8 Safety Limiting Values

Safety limiting(1) intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
DW-16 PACKAGE						
I_S	Safety input, output, or supply current (1)	$R_{\theta JA}$ = 60.3°C/W, V_I = 5.5 V, T_J = 150°C, T_A = 25°C, see 图 5-1			377	mA
		$R_{\theta JA}$ = 60.3°C/W, V_I = 3.6 V, T_J = 150°C, T_A = 25°C, see 图 5-1			576	
		$R_{\theta JA}$ = 60.3°C/W, V_I = 2.75 V, T_J = 150°C, T_A = 25°C, see 图 5-1			754	
P_S	Safety input, output, or total power (1)	$R_{\theta JA}$ = 60.3°C/W, T_J = 150°C, T_A = 25°C, see 图 5-3			2073	mW
T_S	Maximum safety temperature (1)				150	°C
DBQ-16 PACKAGE						
I_S	Safety input, output, or supply current (1)	$R_{\theta JA}$ = 86.5°C/W, V_I = 5.5 V, T_J = 150°C, T_A = 25°C, see 图 5-2			263	mA
		$R_{\theta JA}$ = 86.5°C/W, V_I = 3.6 V, T_J = 150°C, T_A = 25°C, see 图 5-2			401	
		$R_{\theta JA}$ = 86.5°C/W, V_I = 2.75 V, T_J = 150°C, T_A = 25°C, see 图 5-2			525	
P_S	Safety input, output, or total power (1)	$R_{\theta JA}$ = 86.5°C/W, T_J = 150°C, T_A = 25°C, see 图 5-4			1445	mW
T_S	Maximum safety temperature (1)				150	°C

(1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A.
The junction-to-air thermal resistance, $R_{\theta JA}$, in the table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:
$T_J = T_A + R_{\theta JA} \times P$, where P is the power dissipated in the device.
$T_{J(max)} = T_S = T_A + R_{\theta JA} \times P_S$, where $T_{J(max)}$ is the maximum allowed junction temperature.

$P_S = I_S \times V_I$, where V_I is the maximum input voltage.

5.9 Electrical Characteristics—5-V Supply

VCC1 = VCC2 = 5 V ± 10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = -4 mA; See 图 6-1	V_{CCO} (1) - 0.4	4.8		V
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; See 图 6-1		0.2	0.4	V
$V_{IT+(IN)}$	Rising input switching threshold			0.6 x V_{CCI}	0.7 x V_{CCI}	V
$V_{IT-(IN)}$	Falling input switching threshold		0.3 x V_{CCI}	0.4 x V_{CCI}		V
$V_{I(HYS)}$	Input threshold voltage hysteresis		0.1 x V_{CCI}	0.2 x V_{CCI}		V
I_{IH}	High-level input current	V_{IH} = V_{CCI} (1) at INx			10	µA
I_{IL}	Low-level input current	V_{IL} = 0 V at INx	-10			µA
CMTI	Common mode transient immunity	V_I = V_{CCI} or 0 V, V_{CM} = 1200 V; See 图 6-3	85	100		kV/ µ s
C_I	Input Capacitance (2)	V_I = V_{CC}/ 2 + 0.4 × sin(2 π ft), f = 1 MHz, V_{CC} = 5 V		2		pF

(1) V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}
(2) Measured from input pin to same side ground.

5.10 Supply Current Characteristics—5-V Supply

V_{CC1} = V_{CC2} = 5 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO7760							
Supply current - DC signal	V_I = V_{CC1} (ISO7760); V_I = 0 V (ISO7760 with F suffix)		I_{CC1}		1.6	2.9	mA
			I_{CC2}		3	5.3	
	V_I = 0 V (ISO7760); V_I = V_{CC1} (ISO7760 with F suffix)		I_{CC1}		8	11.3	
			I_{CC2}		3.3	5.7	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		5	6.5	
			I_{CC2}		3.5	5.9	
		10 Mbps	I_{CC1}		5.2	6.7	
			I_{CC2}		6.4	9.7	
		100 Mbps	I_{CC1}		7	9.2	
			I_{CC2}		35	47	
ISO7761							
Supply current - DC signal	V_I = V_{CCI} (1)(ISO7761); V_I = 0 V (ISO7761 with F suffix)		I_{CC1}		1.9	3.5	mA
			I_{CC2}		2.9	5.4	
	V_I = 0 V (ISO7761); V_I = V_{CCI} (ISO7761 with F suffix)		I_{CC1}		7.3	10.6	
			I_{CC2}		4.2	6.9	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.7	6.6	
			I_{CC2}		3.8	6.5	
		10 Mbps	I_{CC1}		5.3	8	
			I_{CC2}		6.3	9.6	
		100 Mbps	I_{CC1}		11.5	15.6	
			I_{CC2}		30.5	40.3	
ISO7762							

V_{CC1} = V_{CC2} = 5 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current - DC signal	V_I = V_{CCI} (ISO7762); V_I = 0 V (ISO7762 with F suffix)		I_{CC1}		2.1	4.1	mA
			I_{CC2}		2.6	4.9	
	V_I = 0 V (ISO7762); V_I = V_{CCI} (ISO7762 with F suffix)		I_{CC1}		6.5	9.3	
			I_{CC2}		5	7.6	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.5	6.7	
			I_{CC2}		4	6.5	
		10 Mbps	I_{CC1}		5.6	8	
			I_{CC2}		6	8.9	
		100 Mbps	I_{CC1}		16.5	21.3	
			I_{CC2}		25.7	34	
ISO7763							
Supply current - DC signal	V_I = V_{CCI} (ISO7763); V_I = 0 V (ISO7763 with F suffix)		I_{CC1}, I_{CC2}		2.4	4.7	mA
	V_I = 0 V (ISO7763); V_I = V_{CCI} (ISO7763 with F suffix)		I_{CC1}, I_{CC2}		5.7	8.6	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}, I_{CC2}		4.2	6.8	
		10 Mbps	I_{CC1}, I_{CC2}		5.8	8.7	
		100 Mbps	I_{CC1}, I_{CC2}		21	28.4	

(1) V_{CCI} = Input-side V_{CC}

5.11 Electrical Characteristics—3.3-V Supply

V_{CC1} = V_{CC2} = 3.3 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = -2mA ; See 图 6-1	V_{CCO} (1) - 0.3	3.2		V
V_{OL}	Low-level output voltage	I_{OL} = 2mA ; See 图 6-1		0.1	0.3	V
$V_{IT+(IN)}$	Rising input switching threshold			0.6 x V_{CCI}	0.7 x V_{CCI} (1)	V
$V_{IT-(IN)}$	Falling input switching threshold		0.3 x V_{CCI}	0.4 x V_{CCI}		V
$V_{I(HYS)}$	Input threshold voltage hysteresis		0.1 x V_{CCI}	0.2 x V_{CCI}		V
I_{IH}	High-level input current	V_{IH} = V_{CCI} (1) at INx			10	µA
I_{IL}	Low-level input current	V_{IL} = 0 V at INx	-10			µA
CMTI	Common mode transient immunity	V_I = V_{CC} or 0 V, V_{CM} = 1200 V; See 图 6-3	85	100		kV/us

(1) V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}

5.12 Supply Current Characteristics—3.3-V Supply

V_{CC1} = V_{CC2} = 3.3 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO7760							
Supply current - DC signal	V_I = V_{CC1} (ISO7760); V_I = 0 V (ISO7760 with F suffix)		I_{CC1}		1.6	2.9	mA
			I_{CC2}		3	5.3	
	V_I = 0 V (ISO7760); V_I = V_{CC1} (ISO7760 with F suffix)		I_{CC1}		8	11.4	
			I_{CC2}		3.3	5.7	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.9	6.4	
			I_{CC2}		3.4	5.7	
		10 Mbps	I_{CC1}		5	6.6	
			I_{CC2}		5.5	8.5	
		100 Mbps	I_{CC1}		6.3	8.1	
			I_{CC2}		26	35	
ISO7761							
Supply current - DC signal	V_I = V_{CCI} (1)(ISO7761); V_I = 0 V (ISO7761 with F suffix)		I_{CC1}		1.8	3.5	mA
			I_{CC2}		2.9	5.3	
	V_I = 0 V (ISO7761); V_I = V_{CCI} (ISO7761 with F suffix)		I_{CC1}		7.2	10.3	
			I_{CC2}		4.2	6.9	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.6	6.5	
			I_{CC2}		3.7	6.3	
		10 Mbps	I_{CC1}		5.1	7.5	
			I_{CC2}		5.5	8.6	
		100 Mbps	I_{CC1}		9.4	12.7	
			I_{CC2}		22.8	30.5	
ISO7762							

V_{CC1} = V_{CC2} = 3.3 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current - DC signal	V_I = V_{CCI} (ISO7762); V_I = 0 V (ISO7762 with F suffix)		I_{CC1}		2.1	4	mA
			I_{CC2}		2.5	4.8	
	V_I = 0 V (ISO7762); V_I = V_{CCI} (ISO7762 with F suffix)		I_{CC1}		6.5	9.4	
			I_{CC2}		5	7.5	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.4	6.6	
			I_{CC2}		3.9	6.3	
		10 Mbps	I_{CC1}		5.2	7.5	
			I_{CC2}		5.4	8.1	
		100 Mbps	I_{CC1}		12.9	16.9	
			I_{CC2}		19.5	26	
ISO7763							
Supply current - DC signal	V_I = V_{CCI} (ISO7763); V_I = 0 V (ISO7763 with F suffix)		I_{CC1}, I_{CC2}		2.4	4.6	mA
	V_I = 0 V (ISO7763); V_I = V_{CCI} (ISO7763 with F suffix)		I_{CC1}, I_{CC2}		5.7	8.4	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}, I_{CC2}		4.2	6.6	
		10 Mbps	I_{CC1}, I_{CC2}		5.2	8.1	
		100 Mbps	I_{CC1}, I_{CC2}		16	21.9	

(1) V_{CCI} = Input-side V_{CC}

5.13 Electrical Characteristics—2.5-V Supply

V_{CC1} = V_{CC2} = 2.5 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = -1mA ; See 图 6-1	V_{CCO} (1) - 0.2	2.45		V
V_{OL}	Low-level output voltage	I_{OL} = 1mA ; See 图 6-1		0.05	0.2	V
$V_{IT+(IN)}$	Rising input switching threshold			0.6 x V_{CCI}	0.7 x V_{CCI} (1)	V
$V_{IT-(IN)}$	Falling input switching threshold		0.3 x V_{CCI}	0.4 x V_{CCI}		V
$V_{I(HYS)}$	Input threshold voltage hysteresis		0.1 x V_{CCI}	0.2 x V_{CCI}		V
I_{IH}	High-level input current	V_{IH} = V_{CCI} (1) at INx			10	µA
I_{IL}	Low-level input current	V_{IL} = 0 V at INx	-10			µA
CMTI	Common mode transient immunity	V_I = V_{CC} or 0 V, V_{CM} = 1200 V; See 图 6-3	85	100		kV/us

(1) V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}

5.14 Supply Current Characteristics—2.5-V Supply

V_{CC1} = V_{CC2} = 2.5 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO7760							
Supply current - DC signal	V_I = V_{CC1} (ISO7760); V_I = 0 V (ISO7760 with F suffix)		I_{CC1}		1.6	2.9	mA
			I_{CC2}		3	5.2	
	V_I = 0 V (ISO7760); V_I = V_{CC1} (ISO7760 with F suffix)		I_{CC1}		8	11.6	
			I_{CC2}		3.3	5.7	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.9	6.4	
			I_{CC2}		3.4	5.7	
		10 Mbps	I_{CC1}		5	6.5	
			I_{CC2}		4.9	7.7	
		100 Mbps	I_{CC1}		6	7.7	
			I_{CC2}		20.3	27.9	
ISO7761							
Supply current - DC signal	V_I = V_{CCI} (1) (ISO7761); V_I = 0 V (ISO7761 with F suffix)		I_{CC1}		1.8	3.4	mA
			I_{CC2}		2.9	5.3	
	V_I = 0 V (ISO7761); V_I = V_{CCI} (ISO7761 with F suffix)		I_{CC1}		7.2	10.3	
			I_{CC2}		4.2	6.8	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.6	6.5	
			I_{CC2}		3.7	6.3	
		10 Mbps	I_{CC1}		4.9	7.2	
			I_{CC2}		5	7.9	
		100 Mbps	I_{CC1}		8.3	11.2	
			I_{CC2}		18.1	24.6	
ISO7762							

V_{CC1} = V_{CC2} = 2.5 V ±10% (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current - DC signal	V_I = V_{CCI} (ISO7762); V_I = 0 V (ISO7762 with F suffix)		I_{CC1}		2.1	4	mA
			I_{CC2}		2.6	4.8	
	V_I = 0 V (ISO7762); V_I = V_{CCI} (ISO7762 with F suffix)		I_{CC1}		6.5	9.6	
			I_{CC2}		4.9	7.4	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}		4.4	6.5	
			I_{CC2}		3.9	6.3	
		10 Mbps	I_{CC1}		5	7.2	
			I_{CC2}		5	7.6	
		100 Mbps	I_{CC1}		10.9	14.4	
			I_{CC2}		15.6	21.3	
ISO7763							
Supply current - DC signal	V_I = V_{CCI} (ISO7763); V_I = 0 V (ISO7763 with F suffix)		I_{CC1}, I_{CC2}		2.3	4.6	mA
	V_I = 0 V (ISO7763); V_I = V_{CCI} (ISO7763 with F suffix)		I_{CC1}, I_{CC2}		5.7	8.4	
Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{CC1}, I_{CC2}		4.1	6.6	
		10 Mbps	I_{CC1}, I_{CC2}		4.9	7.6	
		100 Mbps	I_{CC1}, I_{CC2}		13	18.1	

(1) V_{CCI} = Input-side V_{CC}

5.15 Switching Characteristics—5-V Supply

V_{CC1} = V_{CC2} = 5 V ±10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO776x						
t_{PLH}, t_{PHL}	Propagation delay time	See 图 6-1	6	11	17	ns
PWD	Pulse width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$	See 图 6-1		0.4	5.9	ns
$t_{sk(o)}$	Channel-to-channel output skew time(2)	Same-direction channels			4	ns
$t_{sk(pp)}$	Part-to-part skew time(3)				4.5	ns
t_r	Output signal rise time	See 图 6-1		1.1	3.9	ns
t_f	Output signal fall time	See 图 6-1		1.4	3.9	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{CC} goes below 1.7V. See 图 6-2		0.2	0.3	µs
t_{ie}	Time interval error	2^{16} – 1 PRBS data at 100 Mbps		1.3		ns

(1) Also known as pulse skew.
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

5.16 Switching Characteristics—3.3-V Supply

V_{CC1} = V_{CC2} = 3.3 V ±10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO776x						
t_{PLH}, t_{PHL}	Propagation delay time	See 图 6-1	6	12	18.5	ns
PWD	Pulse width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$	See 图 6-1		0.5	5.9	ns
$t_{sk(o)}$	Channel-to-channel output skew time(2)	Same-direction channels			4.4	ns
$t_{sk(pp)}$	Part-to-part skew time(3)				5	ns
t_r	Output signal rise time	See 图 6-1		1	3	ns
t_f	Output signal fall time	See 图 6-1		1	3	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{CC} goes below 1.7V. See 图 6-2		0.2	0.3	μs
t_{ie}	Time interval error	2^{16} – 1 PRBS data at 100 Mbps		1.3		ns

(1) Also known as pulse skew.
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

5.17 Switching Characteristics—2.5-V Supply

V_{CC1} = V_{CC2} = 2.5 V ±10% (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO776x						
t_{PLH}, t_{PHL}	Propagation delay time	See 图 6-1	7.5	13	21	ns
PWD	Pulse width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$			0.6	5.9	ns
$t_{sk(o)}$	Channel-to-channel output skew time(2)	Same-direction channels			4.4	ns
$t_{sk(pp)}$	Part-to-part skew time(3)				5.3	ns
t_r	Output signal rise time	See 图 6-1		1	3.5	ns
t_f	Output signal fall time			1	3.5	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{CC} goes below 1.7V. See 图 6-2		0.1	0.3	µs
t_{ie}	Time interval error	2^{16} – 1 PRBS data at 100 Mbps		1.3		ns

(1) Also known as pulse skew.
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

5.18 Insulation Characteristics Curves

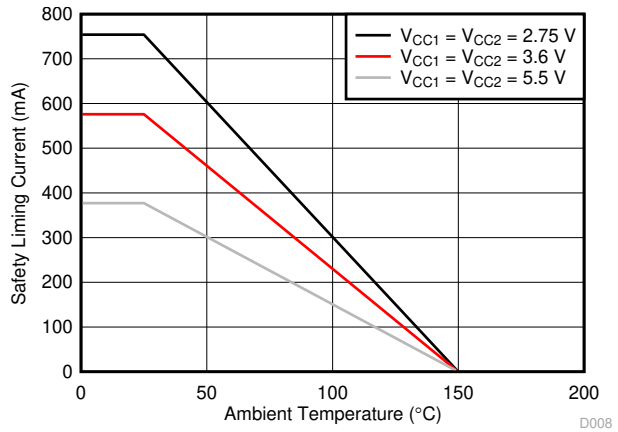


图 5-1. Thermal Derating Curve for Limiting Current per VDE for DW-16 Package

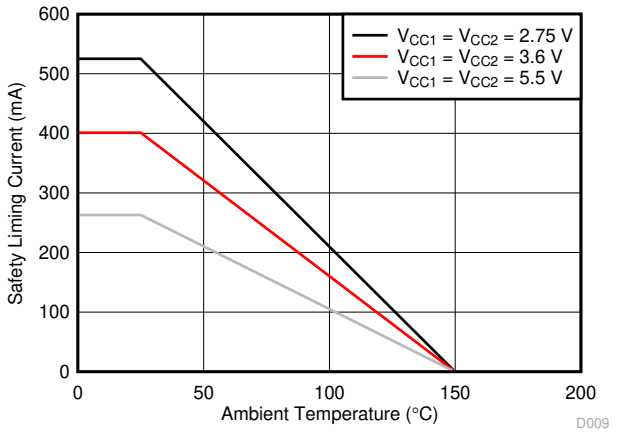


图 5-2. Thermal Derating Curve for Limiting Current per VDE for DBQ-16 Package

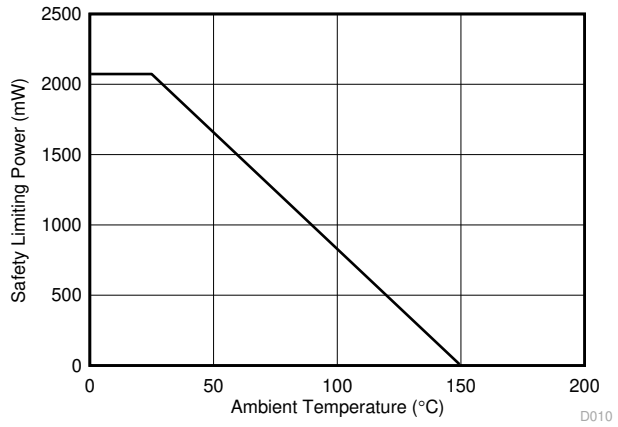


图 5-3. Thermal Derating Curve for Limiting Power per VDE for DW-16 Package

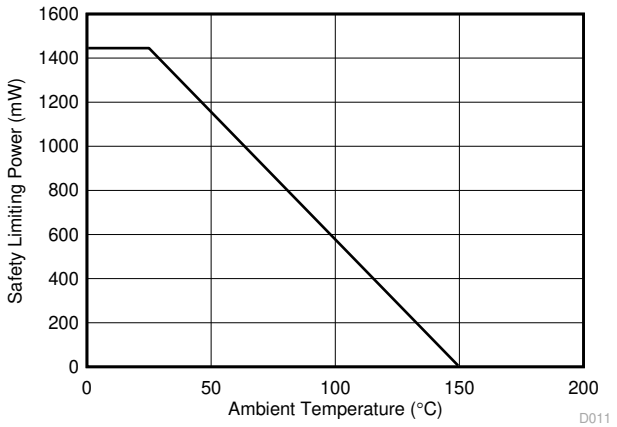
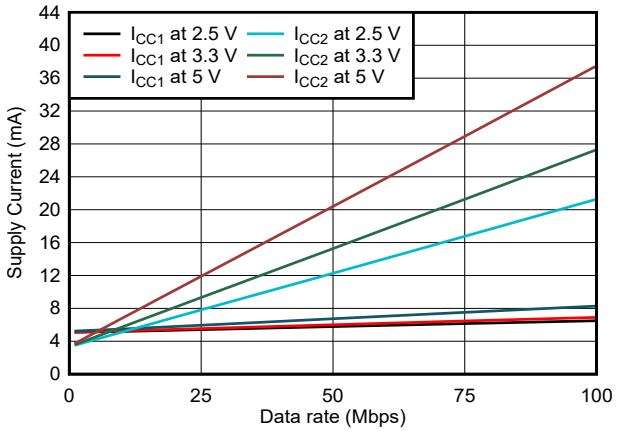


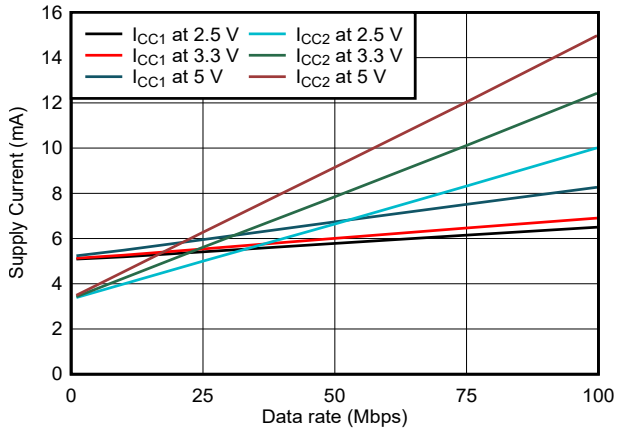
图 5-4. Thermal Derating Curve for Limiting Power per VDE for DBQ-16 Package

5.19 Typical Characteristics



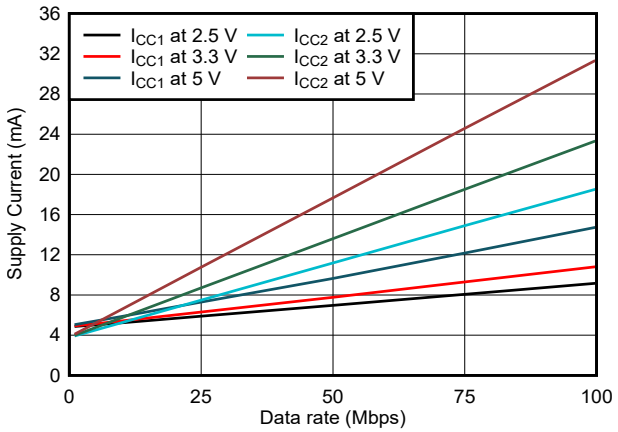
T_A = 25°C C_L = 15 pF

图 5-5. ISO7760 Supply Current vs Data Rate (With 15-pF Load)



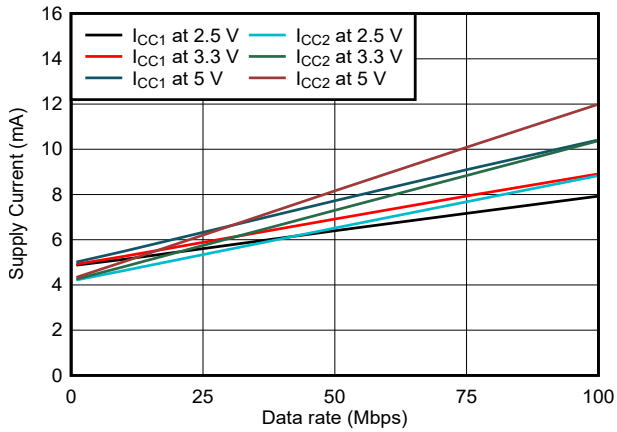
T_A = 25°C C_L = No Load

图 5-6. ISO7760 Supply Current vs Data Rate (With No Load)



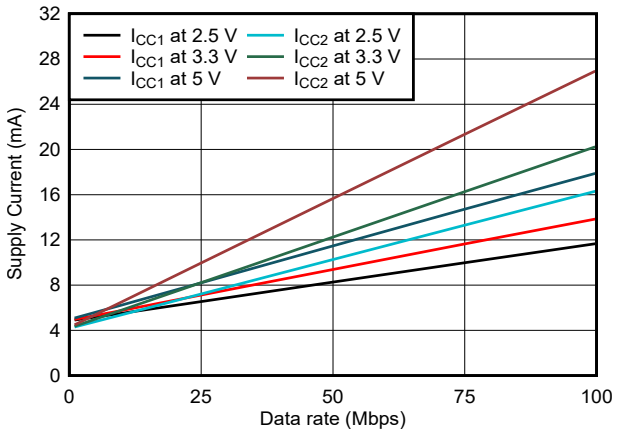
T_A = 25°C C_L = 15 pF

图 5-7. ISO7761 Supply Current vs Data Rate (With 15-pF Load)



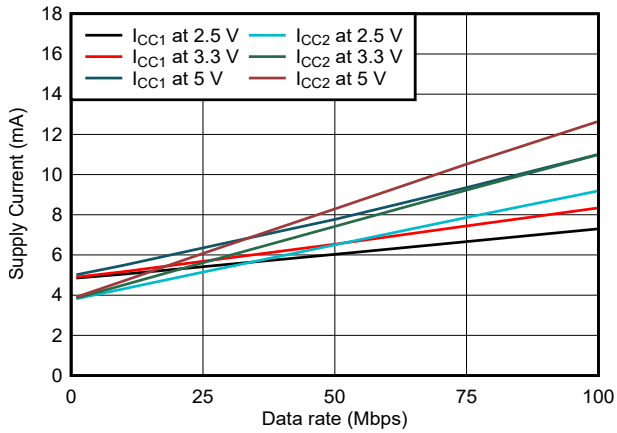
T_A = 25°C C_L = No Load

图 5-8. ISO7761 Supply Current vs Data Rate (With No Load)



T_A = 25°C C_L = 15 pF

图 5-9. ISO7762 Supply Current vs Data Rate (With 15-pF Load)



T_A = 25°C C_L = No Load

图 5-10. ISO7762 Supply Current vs Data Rate (With No Load)

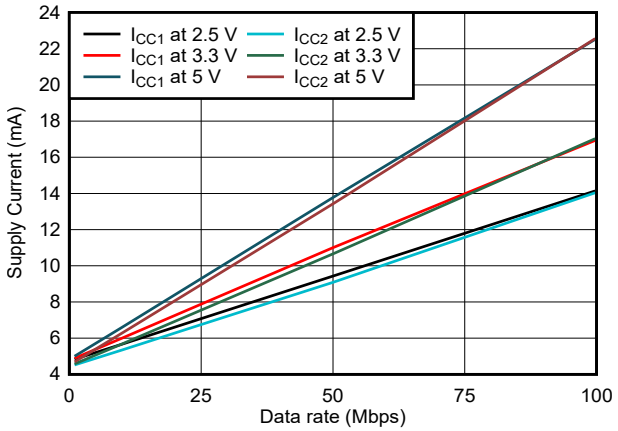


图 5-11. ISO7763 Supply Current vs Data Rate (With 15-pF Load)

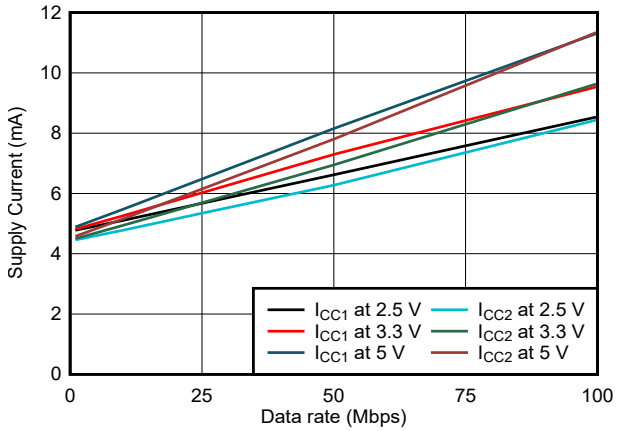


图 5-12. ISO7763 Supply Current vs Data Rate (With No Load)

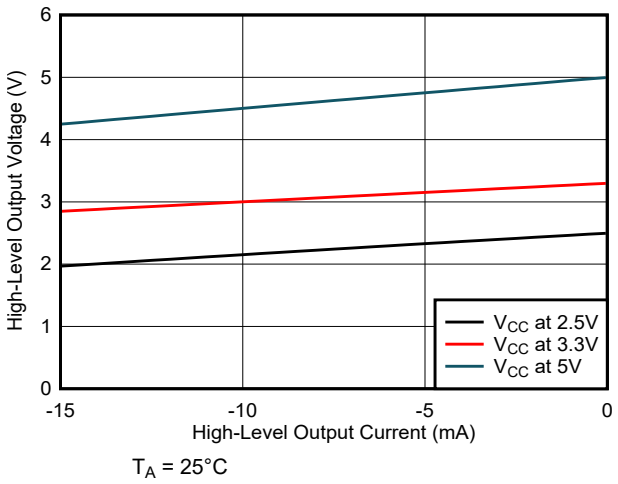


图 5-13. High-Level Output Voltage vs High-Level Output Current

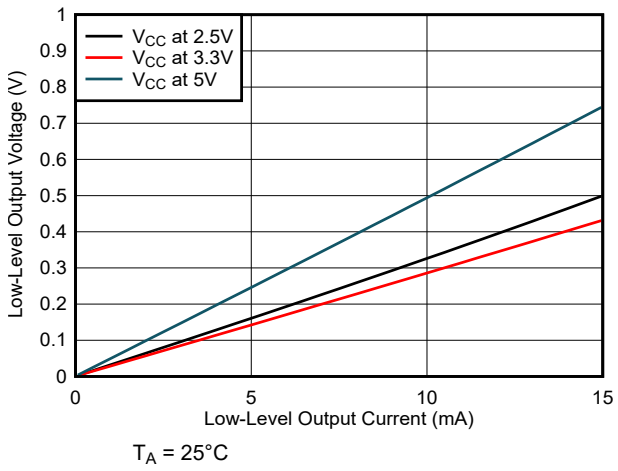


图 5-14. Low-Level Output Voltage vs Low-Level Output Current

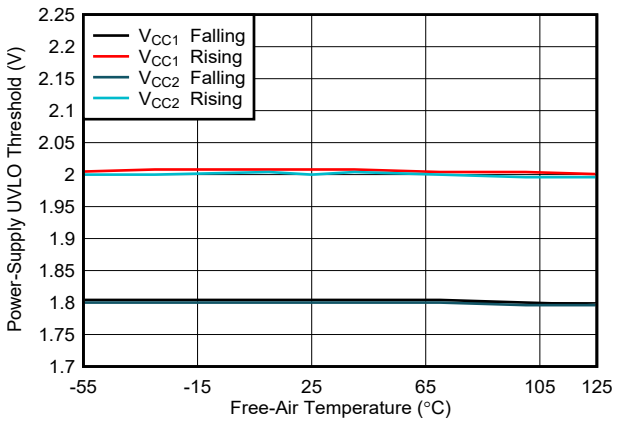


图 5-15. Power Supply Undervoltage Threshold vs Free-Air Temperature

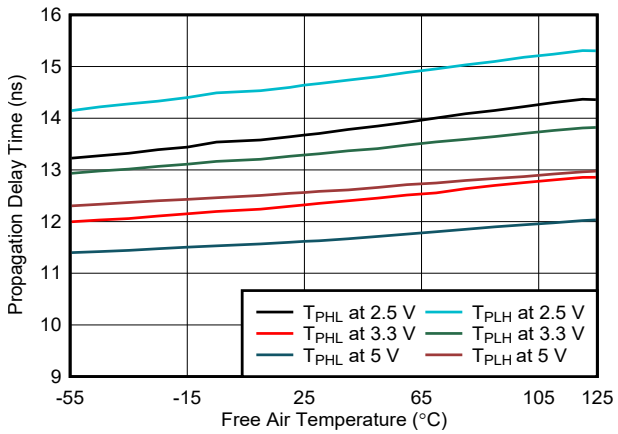
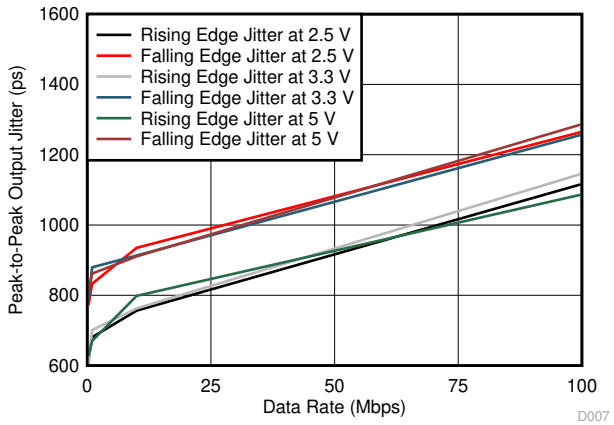


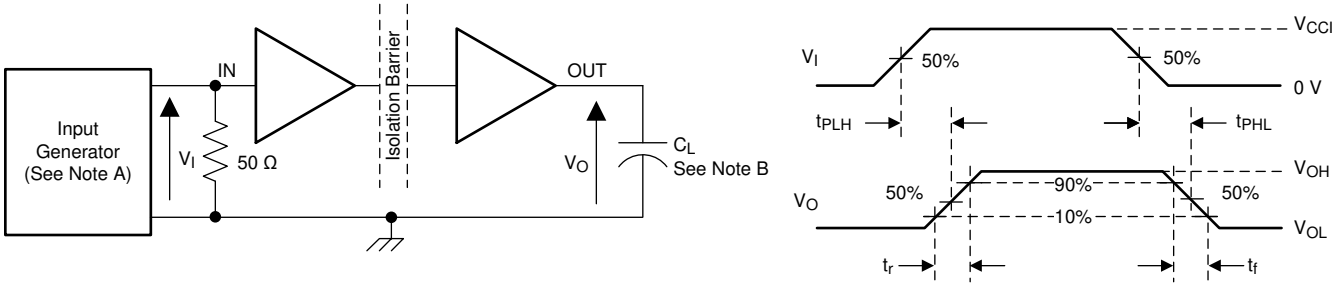
图 5-16. Propagation Delay Time vs Free-Air Temperature



T_A = 25°C

图 5-17. Peak-to-Peak Output Jitter vs Data Rate

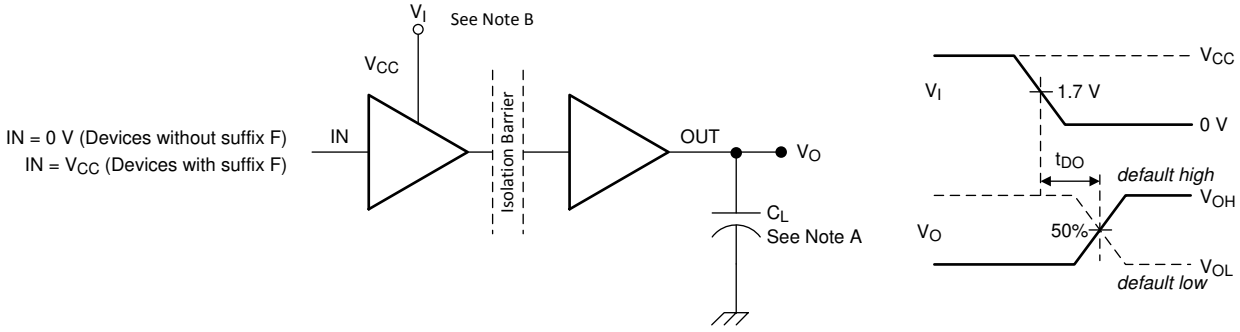
6 Parameter Measurement Information



A. The input pulse is supplied by a generator having the following characteristics: PRR ⩽ 50 kHz, 50% duty cycle, t_r ⩽ 3 ns, t_f ⩽ 3 ns, Z_O = 50 Ω. At the input, a 50-Ω resistor is required to terminate Input Generator signal. It is not needed in actual application.

B. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

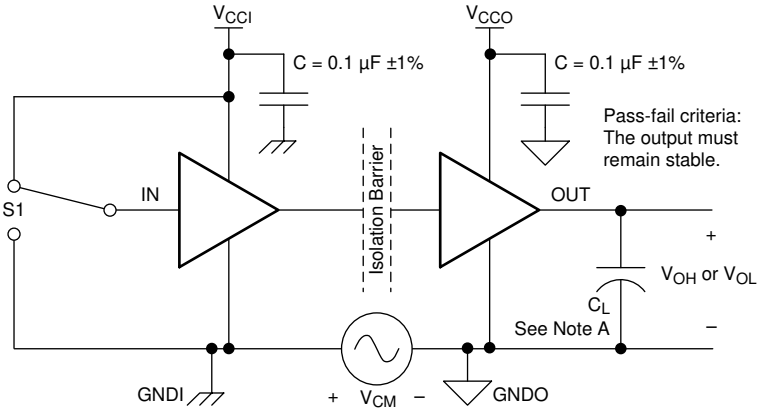
图 6-1. Switching Characteristics Test Circuit and Voltage Waveforms



A. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

B. Power-supply ramp rate = 10 mV/ns

图 6-2. Default Output Delay Time Test Circuit and Voltage Waveforms



A. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

图 6-3. Common-Mode Transient Immunity Test Circuit

7 Detailed Description

7.1 Overview

The ISO776x family of devices uses an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon-dioxide based isolation barrier. The transmitter sends a high-frequency carrier across the barrier to represent one digital state and sends no signal to represent the other digital state. The receiver demodulates the signal after advanced signal conditioning and produces the output through a buffer stage. The ISO776x family of devices also incorporates advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions because of the high-frequency carrier and IO buffer switching. The conceptual block diagram of a digital capacitive isolator, 图 7-1, shows a functional block diagram of a typical channel. 图 7-2 shows a conceptual detail of how the ON-OFF keying scheme works.

7.2 Functional Block Diagram

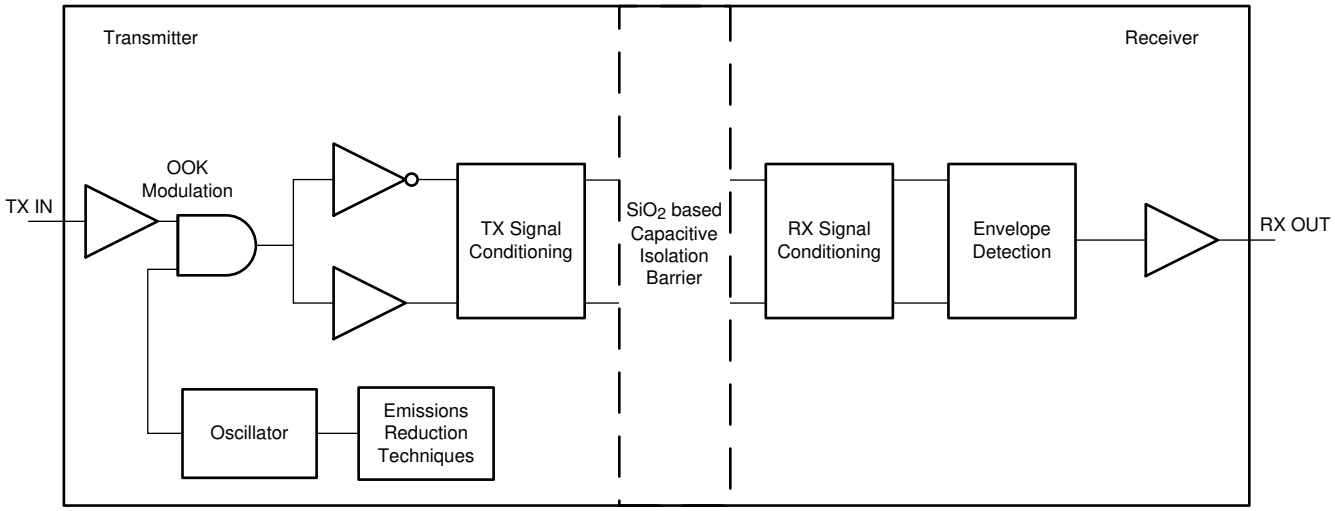


图 7-1. Conceptual Block Diagram of a Digital Capacitive Isolator

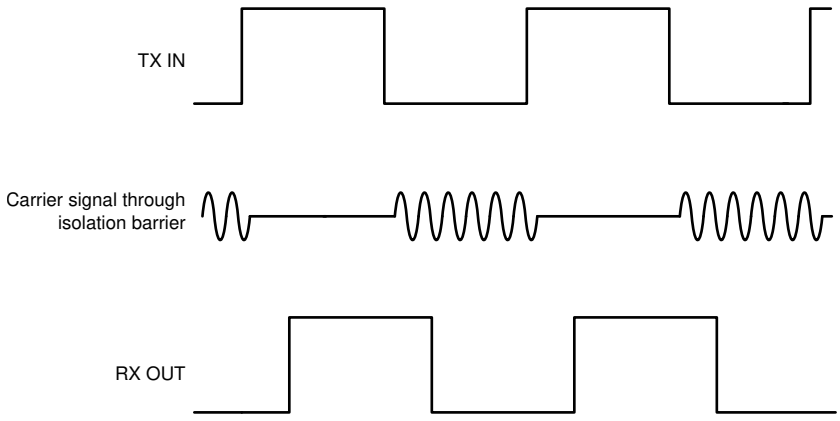


图 7-2. ON-OFF Keying (OOK) Based Modulation Scheme

7.3 Feature Description

表 7-1 lists the device features.

表 7-1. Device Features

PART NUMBER	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT	PACKAGE	RATED ISOLATION(1)
ISO7760	6 Forward, 0 Reverse	100 Mbps	High	DW-16	5000 V_{RMS} / 8000 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7760 with F suffix	6 Forward, 0 Reverse	100 Mbps	Low	DW-16	5000 V_{RMS} / 8000 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7761	5 Forward, 1 Reverse	100 Mbps	High	DW-16	5000 V_{RMS} / 7071 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7761 with F suffix	5 Forward, 1 Reverse	100 Mbps	Low	DW-16	5000 V_{RMS} / 7071 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7762	4 Forward, 2 Reverse	100 Mbps	High	DW-16	5000 V_{RMS} / 7071 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7762 with F suffix	4 Forward, 2 Reverse	100 Mbps	Low	DW-16	5000 V_{RMS} / 7071 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7763	3 Forward, 3 Reverse	100 Mbps	High	DW-16	5000 V_{RMS} / 7071 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}
ISO7763 with F suffix	3 Forward, 3 Reverse	100 Mbps	Low	DW-16	5000 V_{RMS} / 7071 V_{PK}
				DBQ-16	3000 V_{RMS} / 4242 V_{PK}

(1) See 节 5.7 for detailed isolation ratings.

7.3.1 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO776x family of devices incorporates many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.
- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.

7.4 Device Functional Modes

表 7-2 lists the functional modes for the ISO776x.

表 7-2. Function Table

V_{CCI}	V_{CCO}	INPUT (INx)(2)	OUTPUT (OUTx)	COMMENTS
PU	PU	H	H	Normal Operation: A channel output assumes the logic state of the input.
		L	L	
		Open	Default	Default mode: When INx is open, the corresponding channel output goes to its default logic state. Default is *High* for ISO776x and *Low* for ISO776x with F suffix.
PD	PU	X	Default	Default mode: When V_{CCI} is unpowered, a channel output assumes the logic state based on the selected default option. Default is *High* for ISO776x and *Low* for ISO776x with F suffix. When V_{CCI} transitions from unpowered to powered-up, a channel output assumes the logic state of its input. When V_{CCI} transitions from powered-up to unpowered, channel output assumes the selected default state.
X	PD	X	Undetermined	When V_{CCO} is unpowered, a channel output is undetermined (1). When V_{CCO} transitions from unpowered to powered-up, a channel output assumes the logic state of the input

(1) The outputs are in undetermined state when 1.7 V < V_{CCI}, V_{CCO} < 2.25 V.
(2) A strongly driven input signal can weakly power the floating V_{CC} via an internal protection diode and cause undetermined output.

7.4.1 Device I/O Schematics

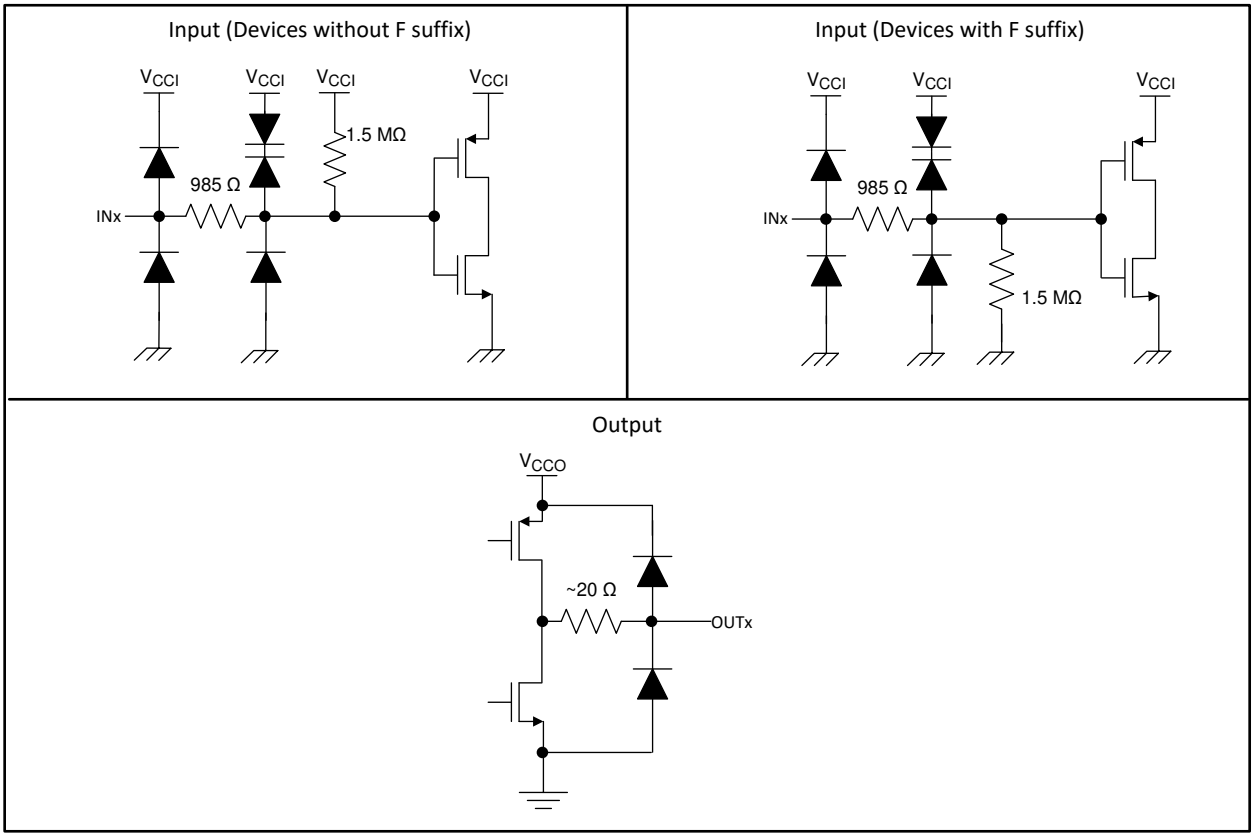


图 7-3. Device I/O Schematics

8 Application and Implementation

备注

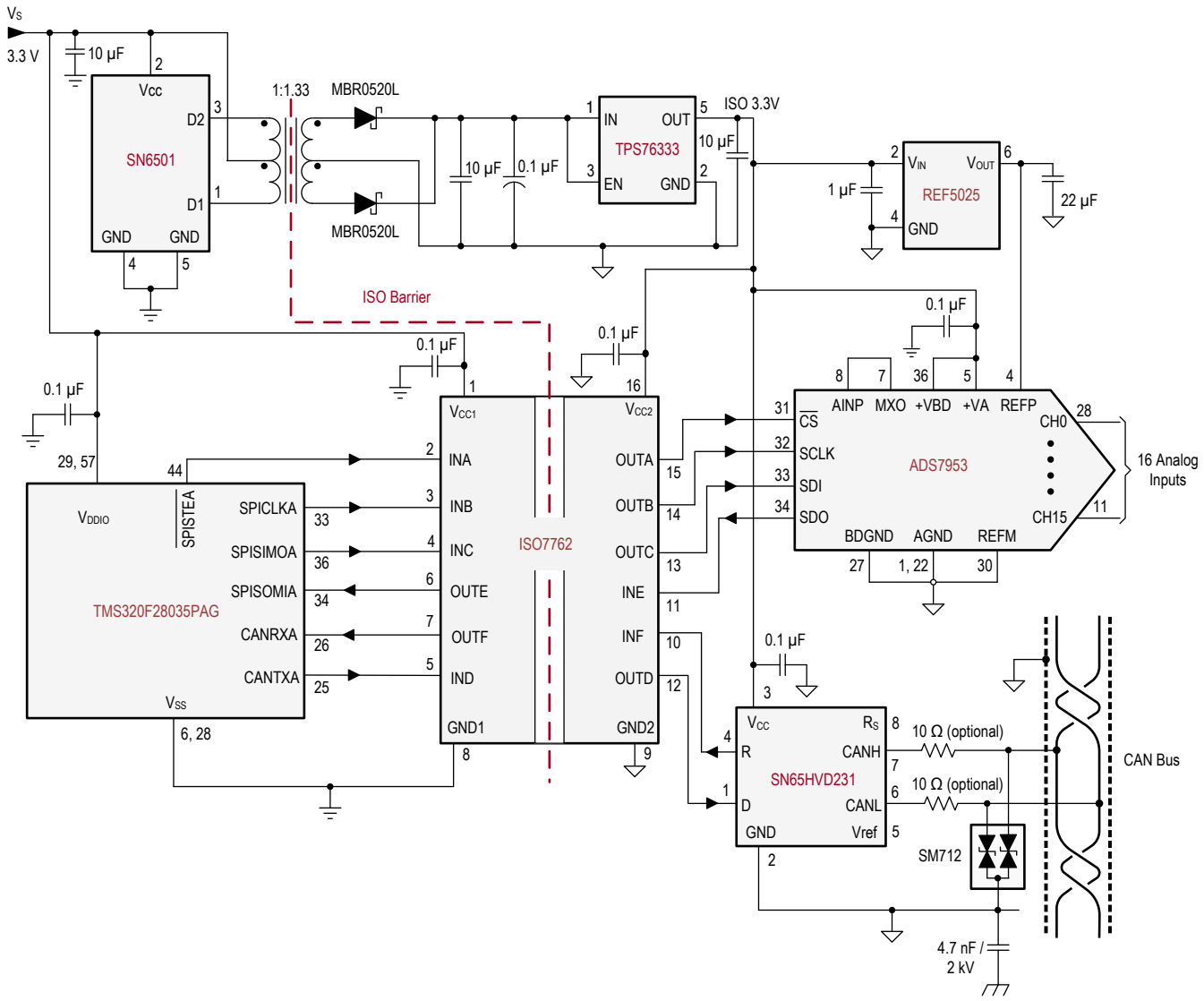
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI’s customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The ISO776x family of devices is a high-performance, six-channel digital isolators. The ISO776x family of devices uses single-ended CMOS-logic switching technology. The voltage range is from 2.25 V to 5.5 V for both supplies, V_{CC1} and V_{CC2}. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is, µC or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

8.2 Typical Application

图 8-1 shows the isolated serial-peripheral interface (SPI) and controller-area network (CAN) interface implementation.



Multiple pins and discrete components omitted for clarity purpose.

图 8-1. Isolated SPI and CAN Interface

8.2.1 Design Requirements

For this design example, use the parameters listed in 表 8-1.

表 8-1. Design Parameters

PARAMETER	VALUE
Supply voltage, V_{CC1} and V_{CC2}	2.25 to 5.5 V
Decoupling capacitor between V_{CC1} and GND1	0.1 µF
Decoupling capacitor from V_{CC2} and GND2	0.1 µF

8.2.2 Detailed Design Procedure

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the ISO776x family of devices only requires two external bypass capacitors to operate.

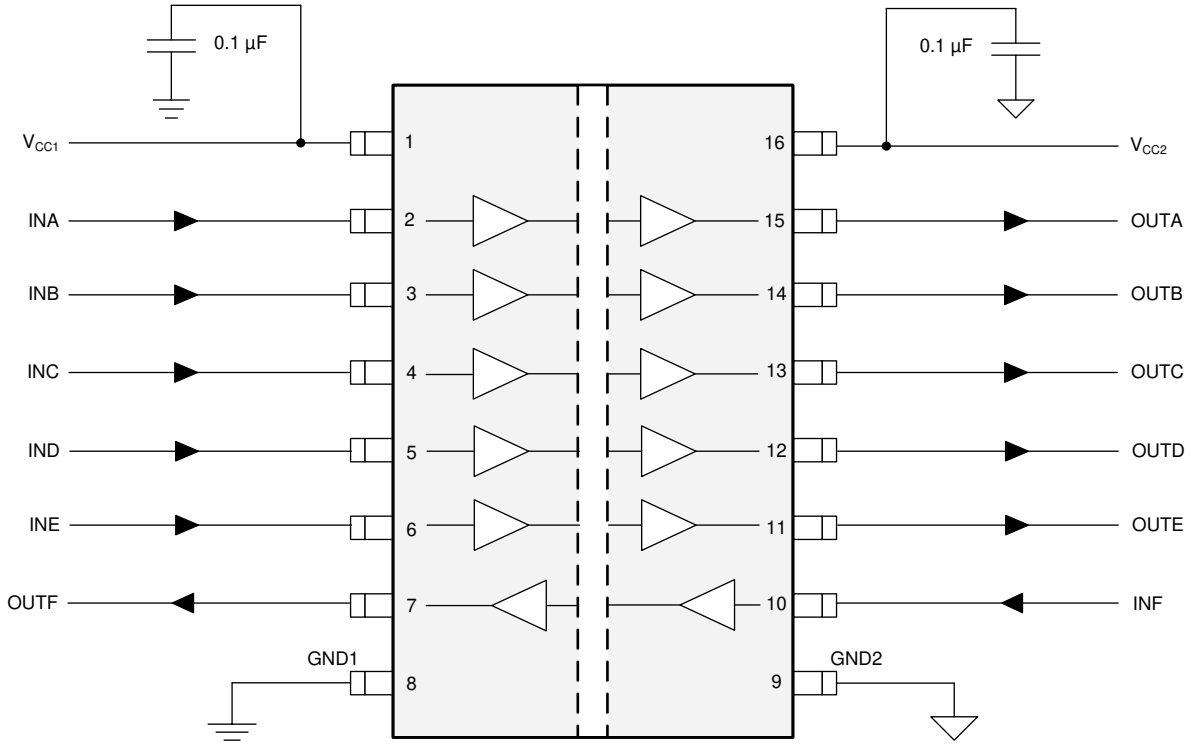


图 8-2. Typical ISO7761 Circuit Hook-up

8.2.3 Application Curves

The typical eye diagram of the ISO776x family of devices indicates low jitter and a wide open eye at the maximum data rate of 100 Mbps.

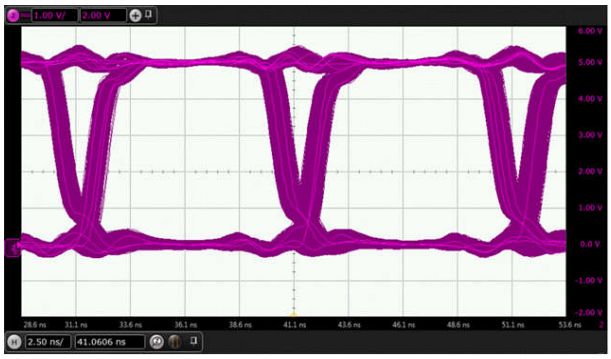


图 8-3. Eye Diagram at 100 Mbps PRBS 2^{16} – 1 Data, 5 V and 25°C

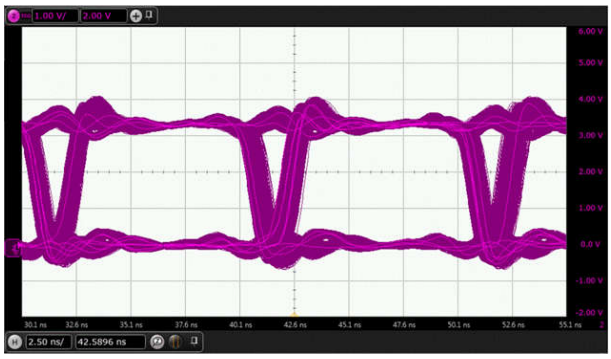


图 8-4. Eye Diagram at 100 Mbps PRBS 2^{16} – 1 Data, 3.3 V and 25°C

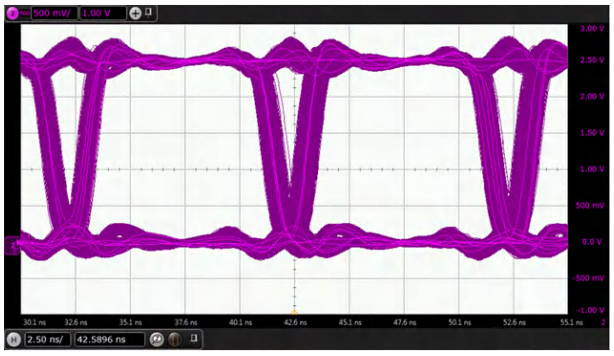


图 8-5. Eye Diagram at 100 Mbps PRBS 2^{16} – 1 Data, 2.5 V and 25°C

8.2.3.1 Insulation Lifetime

Insulation lifetime projection data is collected by using industry-standard Time Dependent Dielectric Breakdown (TDDB) test method. In this test, all pins on each side of the barrier are tied together creating a two-terminal device and high voltage applied between the two sides; See 图 8-6for TDDB test setup. The insulation breakdown data is collected at various high voltages switching at 60 Hz over temperature. For reinforced insulation, VDE standard requires the use of TDDB projection line with failure rate of less than 1 part per million (ppm). Even though the expected minimum insulation lifetime is 20 years at the specified working isolation voltage, VDE reinforced certification requires additional safety margin of 20% for working voltage and 50% for lifetime which translates into minimum required insulation lifetime of 30 years at a working voltage that's 20% higher than the specified value.

图 8-7 shows the intrinsic capability of the isolation barrier to withstand high voltage stress over its lifetime. Based on the TDDB data, the intrinsic capability of the insulation is 1500 V_{RMS} with a lifetime of 36 years. Other factors, such as package size, pollution degree, material group, etc. can further limit the working voltage of the component. The working voltage of DW-16 package is specified upto 1500 V_{RMS} and DBQ-16 package up to 400 V_{RMS}. At the lower working voltages, the corresponding insulation lifetime is much longer than 36 years.

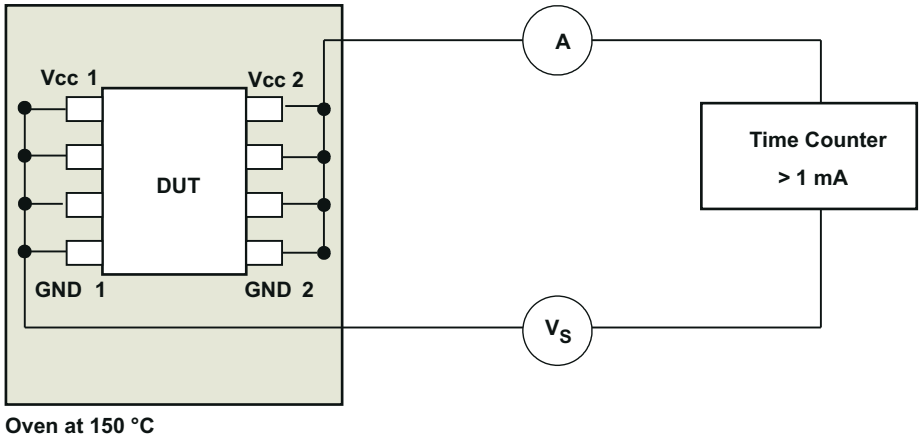


图 8-6. Test Setup for Insulation Lifetime Measurement

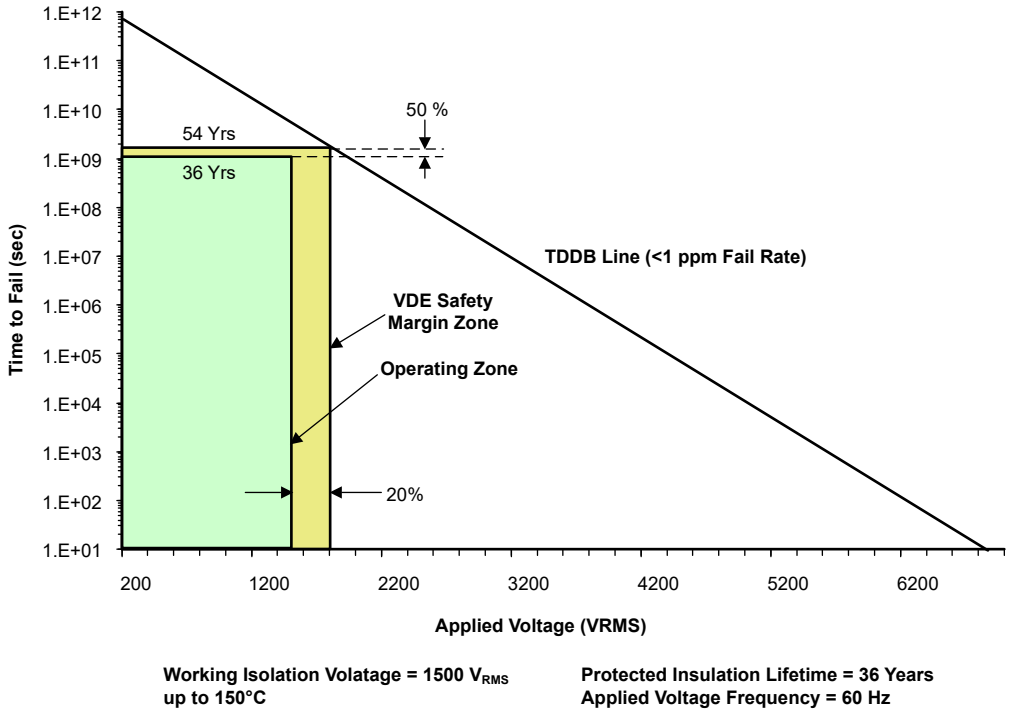


图 8-7. Insulation Lifetime Projection Data

9 Power Supply Recommendations

To help ensure reliable operation at data rates and supply voltages, a 0.1- μ F bypass capacitor is recommended at input and output supply pins (V_{CC1} and V_{CC2}). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' SN6501 or SN6505. For such applications, detailed power supply design and transformer selection recommendations are available in the *SN6501 Transformer Driver for Isolated Power Supplies* data sheet or the *SN6505 Low-Noise 1-A Transformer Drivers for Isolated Power Supplies* data sheet.

10 Layout

10.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see 图 10-1). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/inch^2.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, see the *Digital Isolator Design Guide* application report.

10.1.1 PCB Material

For digital circuit boards operating at less than 150 Mbps, (or rise and fall times greater than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

10.2 Layout Example

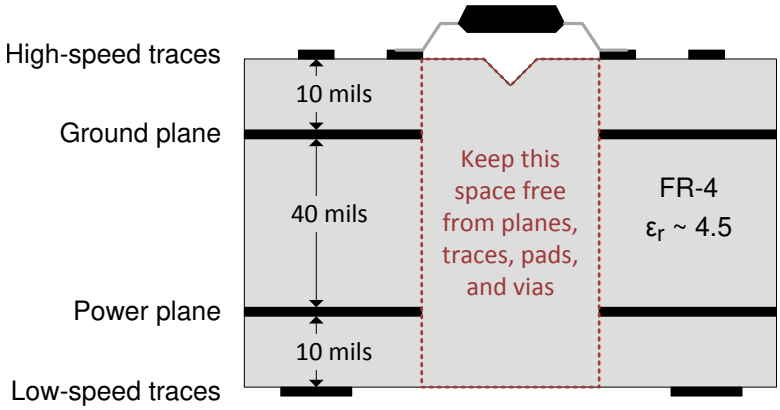


图 10-1. Layout Example Schematic

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *Digital Isolator Design Guide* application report
- Texas Instruments, *How to use isolation to improve ESD, EFT and Surge immunity in industrial systems* application report
- Texas Instruments, *Isolation Glossary*
- Texas Instruments, *TMS320F2803xPiccolo™ Microcontrollers* data sheet
- Texas Instruments, *ADS79xx 12/10/8-Bit, 1 MSPS, 16/12/8/4-Channel, Single-Ended, MicroPower, Serial Interface ADCs* data sheet
- Texas Instruments, *REF50xx Low-Noise, Very Low Drift, Precision Voltage Reference* data sheet
- Texas Instruments, *SN6501 Transformer Driver for Isolated Power Supplies* data sheet
- Texas Instruments, *SN65HVD23x 3.3-V CAN Bus Transceivers* data sheet
- Texas Instruments, *TPS76333 Low-Power 150-mA Low-Dropout Linear Regulators* data sheet

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Community Resources

11.4 Trademarks

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12 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision G (June 2023) to Revision H (January 2024)	Page
• 更新了整个文档中的表、图和交叉参考的编号格式	1
• Updated Thermal Characteristics, Safety Limiting Values, and Thermal Derating Curves to provide more accurate system-level thermal calculations	6
• Updated electrical and switching characteristics to match device performance	6

Changes from Revision F (November 2022) to Revision G (June 2023)	Page
• 将整个文档中的标准名称从“DIN V VDE V 0884-11:2017-01”更改为“DIN EN IEC 60747-17 (VDE 0884-17)”	1
• 通篇删除了对标准 IEC/EN/CSA 60950-1 的引用	1
• 通篇删除了所有标准名称中的标准版本和年份参考	1
• Added Maximum impulse voltage (V_{IMP}) per DIN EN IEC 60747-17 (VDE 0884-17)	9
• Changed test conditions and values of Maximum surge isolation voltage (V_{IOSM}) specification per DIN EN IEC 60747-17 (VDE 0884-17)	9
• Clarified method b test conditions of Apparent charge (q_{PD})	9
• Changed maximum working voltage value From: 250 V_{RMS} To: 400 V_{RMS} for DBQ-16 devices per GB 4943.1	11

- Changed working voltage lifetime margin from: 87.5% to: 50%, minimum required insulation lifetime from: 37.5 years to: 30 years and insulation lifetime per TDDB from: 135 years to: 169 years per DIN EN IEC 60747-17 (VDE 0884-17)..... 33
- Changed 图 8-7 per DIN EN IEC 60747-17 (VDE 0884-17)..... 33

Changes from Revision E (February 2019) to Revision F (November 2022) **Page**

- 更新了整个文档中的表格、图和交叉参考的编号格式.....1

Changes from Revision D (November 2018) to Revision E (February 2019) **Page**

- Changed CPG parameter description from "External clearance" to "External creepage"..... 9

Changes from Revision C (January 2018) to Revision D (November 2018) **Page**

- 通篇进行了编辑性和修饰性更改.....1
- 将“隔离栅寿命：>40 年”更改为“预计寿命超过 100 年”（位于节 1）.....1
- 在节 1 中添加了“隔离等级高达 5000V_{RMS}”.....1
- 在节 1 中添加了“浪涌能力高达 12.8kV”.....1
- 在节 1 中添加了“在整个隔离栅具有 ±8kV IEC 61000-4-2 接触放电保护”.....1
- 添加了“提供汽车版本：ISO776x-Q1”（位于节 1）.....1
- 通篇删除了“计划的认证”这一表述.....1
- 更新了节 2 列表.....1
- 更改了图 3-1 以显示串联隔离电容器.....1
- Added table note to Data rate specification.....7
- Changed V_{IORM} value for DW-16 package from "1414 V_{PK}" to "2121 V_{PK} 9
- Changed V_{IOWM} values for DW-16 package from "1000 V_{RMS}" and "1414 V_{DC}" to "1500 V_{RMS}" and "2121 V_{DC}".....9
- Updated certification information..... 11
- Changed From: "*Table 2*" To: "*Safety Related Certifications*" in 表 7-1 table note..... 28
- Changed 图 7-3 29
- Added 节 8.2.3.1 sub-section under 节 8.2.3 section.....33

Changes from Revision B (November 2017) to Revision C (January 2018) **Page**

- Changed the C_{IO} value for the DBQ package from 1.1 to 0.9 pF.....9

Changes from Revision A (August 2017) to Revision B (November 2017) **Page**

- 更改了*特性*和*安全相关认证*表中的 CSA 认证措辞.....1
- 将 DBQ-16 封装的隔离电压从 2500 更改为 3000V_{RMS} 1
- Added the maximum transient isolation voltage for the DW-16 package of the ISO7761, ISO7762, and ISO7763 devices and changed the maximum value for the DBQ-16 package from 3600 to 4242 for all devices.....9
- Changed table note and table condition of safety limiting values..... 11
- Added the supply current vs data rate graphs for the ISO7761, ISO7762, and ISO7763 in the *Typical Characteristics* section.....23

Changes from Revision * (August 2017) to Revision A (August 2017)	Page
• Deleted EN from the *Common-Mode Transient Immunity Test Circuit* figure	26
• Changed the V_{CC1} and V_{CC2} signals in the *Typical ISO7761 Circuit Hook-up* figure	31

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISO7760DBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7760
ISO7760DBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7760
ISO7760DWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7760
ISO7760DWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7760
ISO7760FDBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7760F
ISO7760FDBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7760F
ISO7760FDWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7760F
ISO7760FDWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7760F
ISO7761DBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7761
ISO7761DBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7761
ISO7761DWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7761
ISO7761DWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7761
ISO7761FDBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7761F
ISO7761FDBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7761F
ISO7761FDWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7761F
ISO7761FDWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7761F
ISO7761FSDBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-55 to 125	7761FS
ISO7762DBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762
ISO7762DBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762
ISO7762DBQRG4	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762
ISO7762DBQRG4.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762
ISO7762DWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7762
ISO7762DWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7762
ISO7762FDBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762F
ISO7762FDBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762F
ISO7762FDBQRG4	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762F
ISO7762FDBQRG4.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7762F
ISO7762FDWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7762F
ISO7762FDWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7762F

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISO7762FSDBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-55 to 125	7762FS
ISO7763DBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7763
ISO7763DBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7763
ISO7763DWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7763
ISO7763DWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7763
ISO7763FDBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7763F
ISO7763FDBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7763F
ISO7763FDBQRG4	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7763F
ISO7763FDBQRG4.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7763F
ISO7763FDWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7763F
ISO7763FDWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7763F

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF ISO7760, ISO7761, ISO7762, ISO7763 :

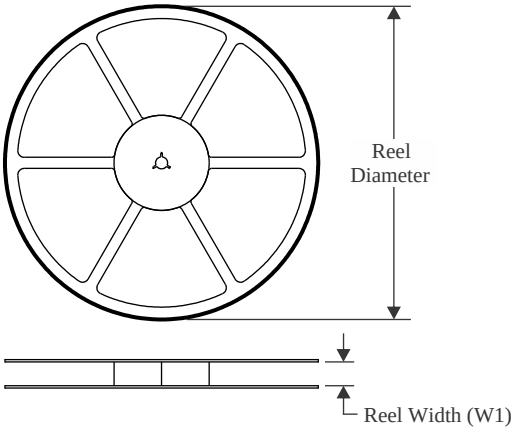
- Automotive : ISO7760-Q1, ISO7761-Q1, ISO7762-Q1, ISO7763-Q1

NOTE: Qualified Version Definitions:

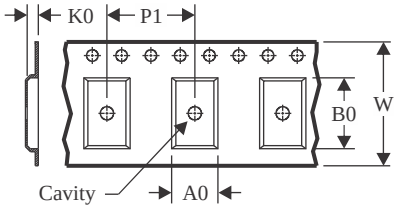
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

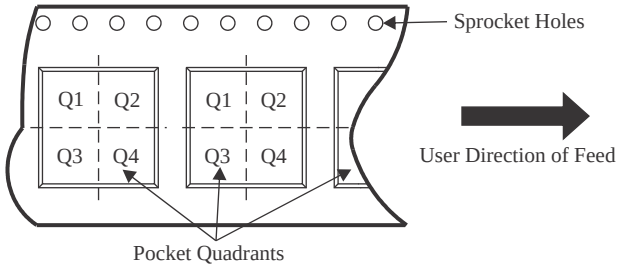


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

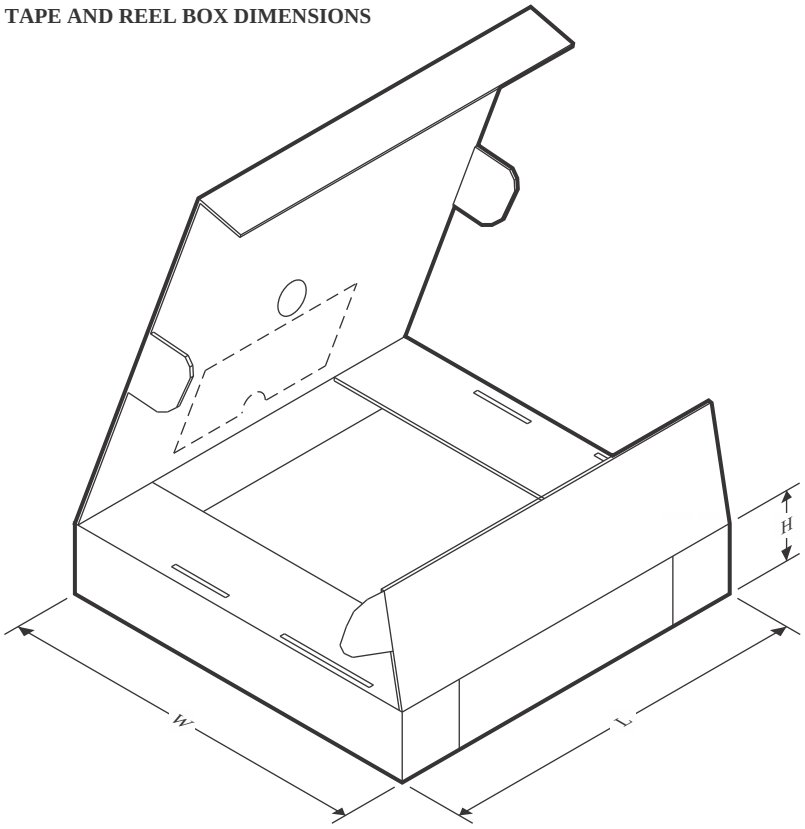


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7760DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7760DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7760DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7760FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7760FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7760FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7760FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7761DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7761DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7761DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7761DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7761FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7761FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7761FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7761FSDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7762DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7762DBQRG4	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7762DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7762DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7762FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7762FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7762FDBQRG4	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7762FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7762FSDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7763DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7763DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7763DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7763FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7763FDBQRG4	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7763FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7763FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7760DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7760DWR	SOIC	DW	16	2000	353.0	353.0	32.0
ISO7760DWR	SOIC	DW	16	2000	356.0	356.0	36.0
ISO7760FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7760FDBQR	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7760FDWR	SOIC	DW	16	2000	356.0	356.0	36.0
ISO7760FDWR	SOIC	DW	16	2000	353.0	353.0	32.0
ISO7761DBQR	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7761DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7761DWR	SOIC	DW	16	2000	353.0	353.0	32.0
ISO7761DWR	SOIC	DW	16	2000	356.0	356.0	36.0
ISO7761FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7761FDBQR	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7761FDWR	SOIC	DW	16	2000	353.0	353.0	32.0
ISO7761FSDBQR	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7762DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7762DBQRG4	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7762DWR	SOIC	DW	16	2000	353.0	353.0	32.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7762DWR	SOIC	DW	16	2000	356.0	356.0	36.0
ISO7762FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7762FDBQR	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7762FDBQRG4	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7762FDWR	SOIC	DW	16	2000	353.0	353.0	32.0
ISO7762FSDBQR	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7763DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7763DWR	SOIC	DW	16	2000	353.0	353.0	32.0
ISO7763DWR	SOIC	DW	16	2000	356.0	356.0	36.0
ISO7763FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO7763FDBQRG4	SSOP	DBQ	16	2500	350.0	350.0	43.0
ISO7763FDWR	SOIC	DW	16	2000	356.0	356.0	36.0
ISO7763FDWR	SOIC	DW	16	2000	353.0	353.0	32.0

GENERIC PACKAGE VIEW

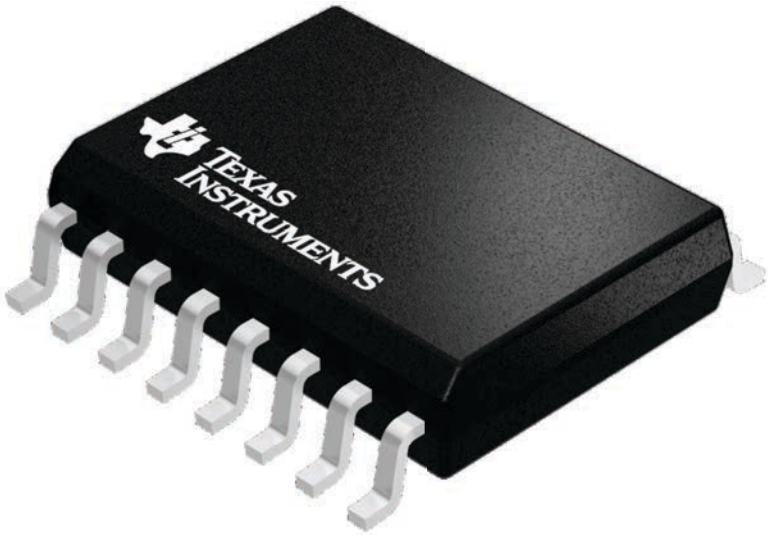
DW 16

SOIC - 2.65 mm max height

7.5 x 10.3, 1.27 mm pitch

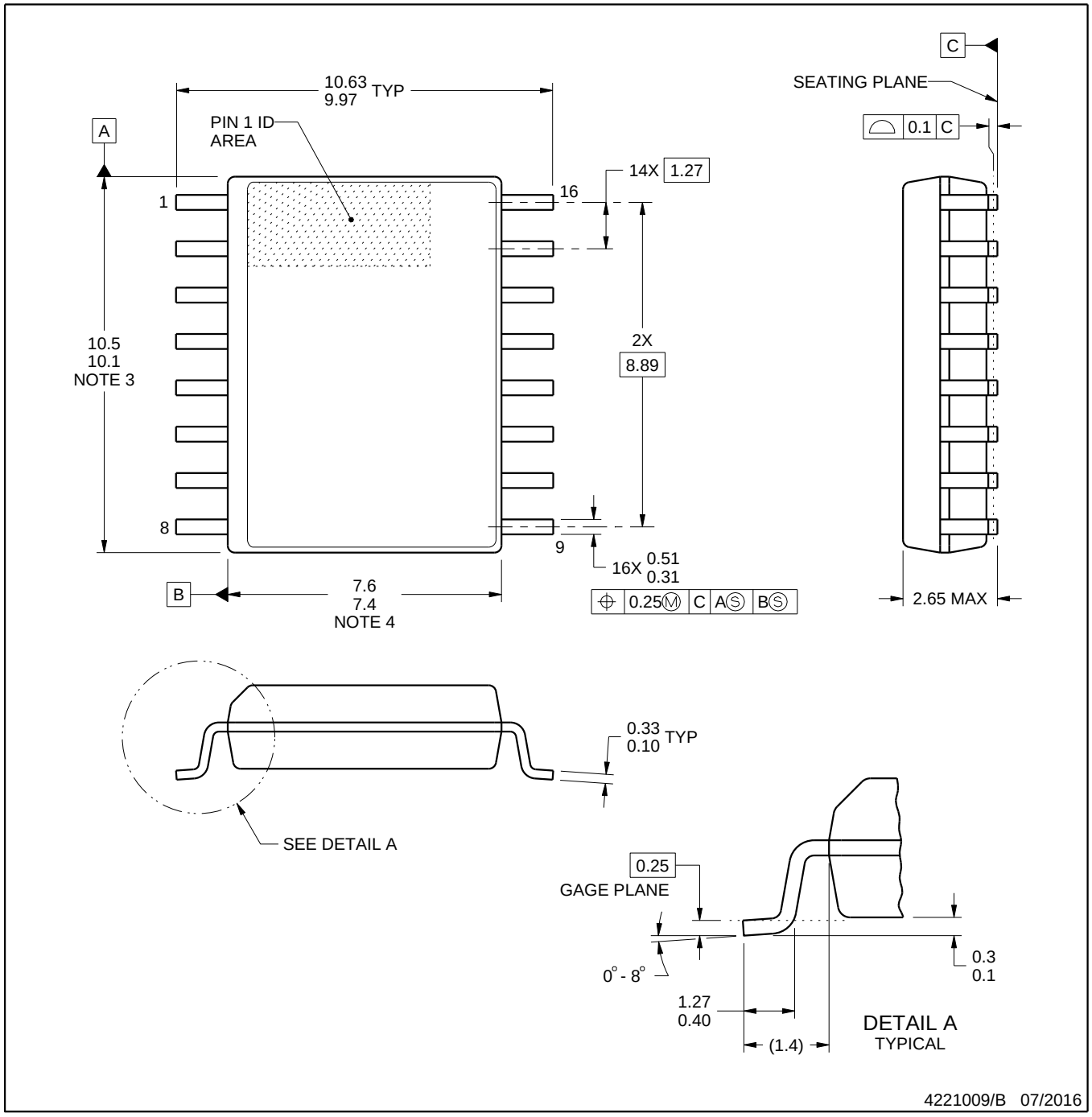
SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



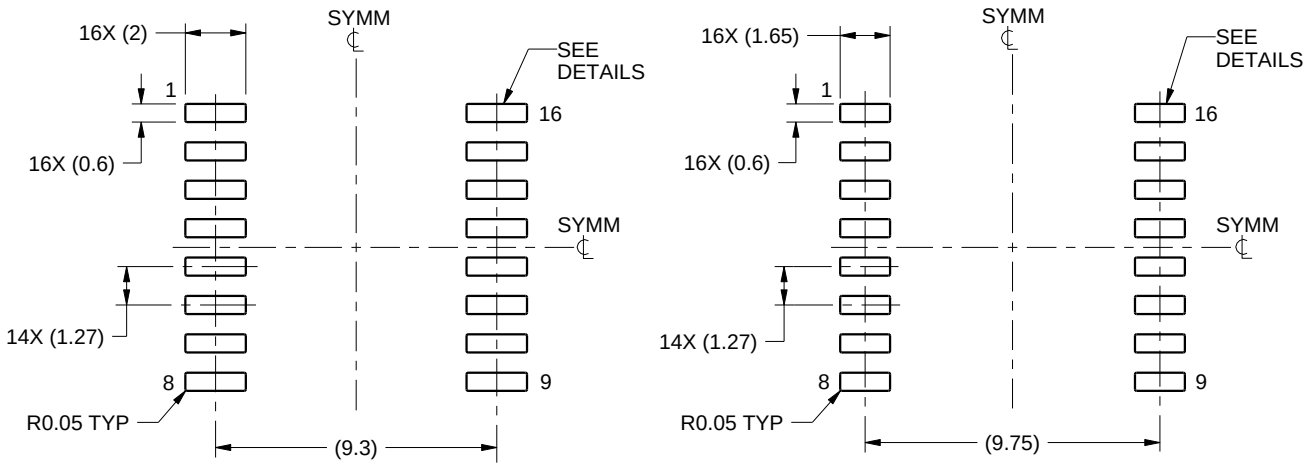
4224780/A

SOIC



NOTES:

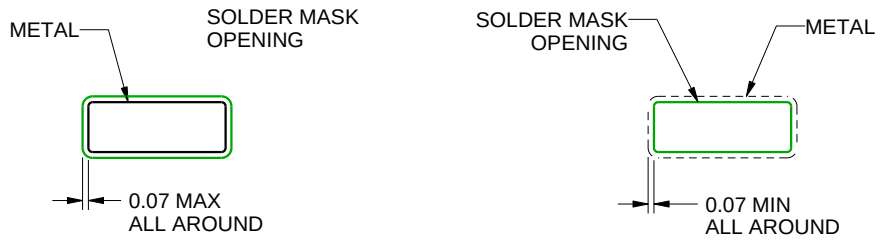
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.



IPC-7351 NOMINAL
7.3 mm CLEARANCE/CREEPAGE

HV / ISOLATION OPTION
8.1 mm CLEARANCE/CREEPAGE

LAND PATTERN EXAMPLE
SCALE:4X



NON SOLDER MASK DEFINED

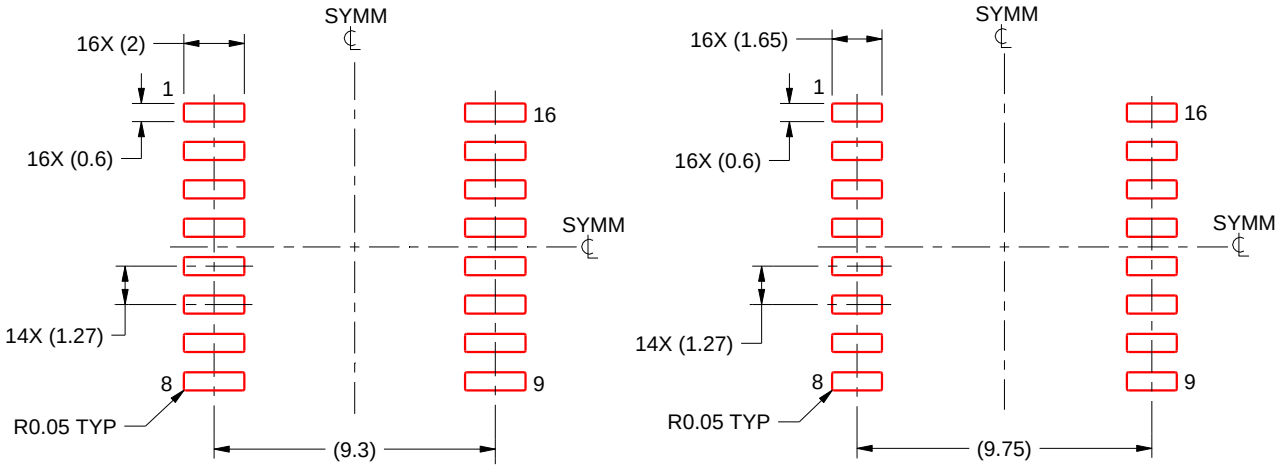
SOLDER MASK DEFINED

SOLDER MASK DETAILS

4221009/B 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



IPC-7351 NOMINAL
7.3 mm CLEARANCE/CREEPAGE

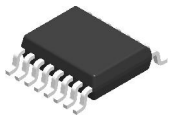
HV / ISOLATION OPTION
8.1 mm CLEARANCE/CREEPAGE

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:4X

4221009/B 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

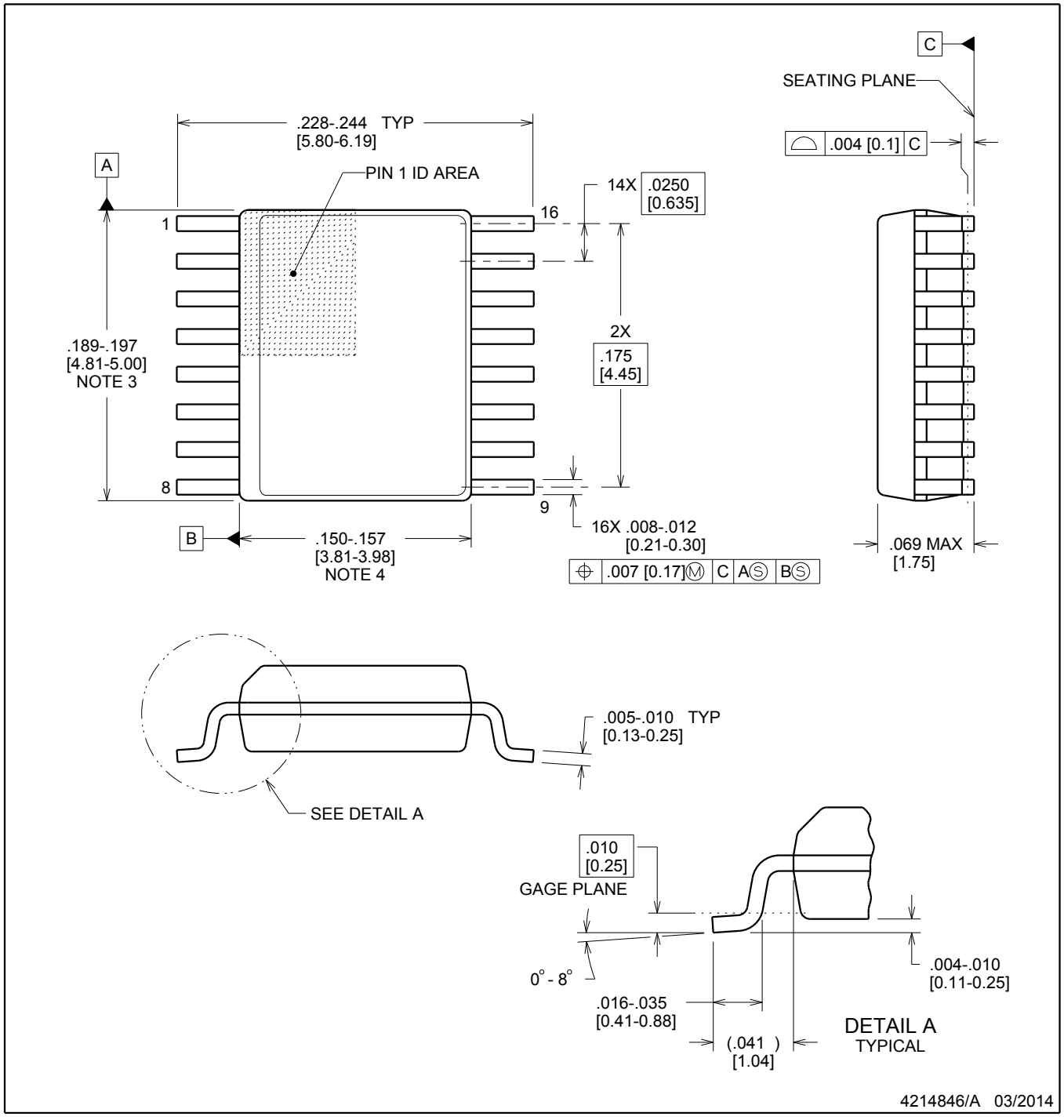


PACKAGE OUTLINE

DBQ0016A

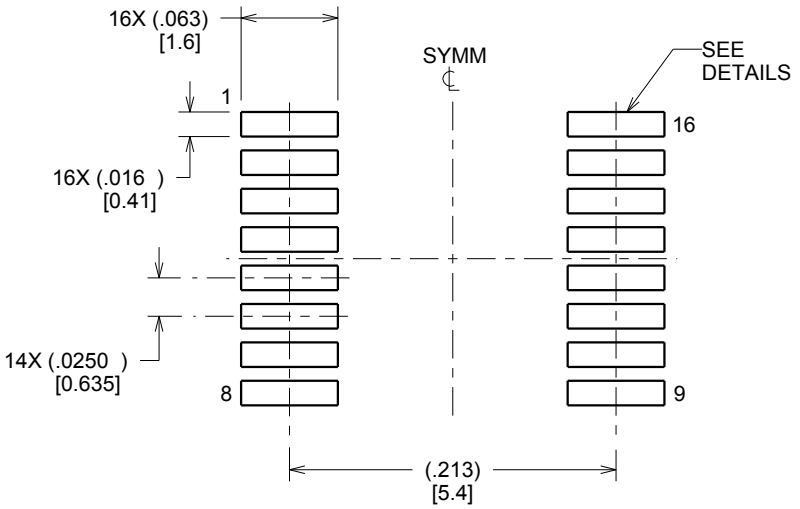
SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE

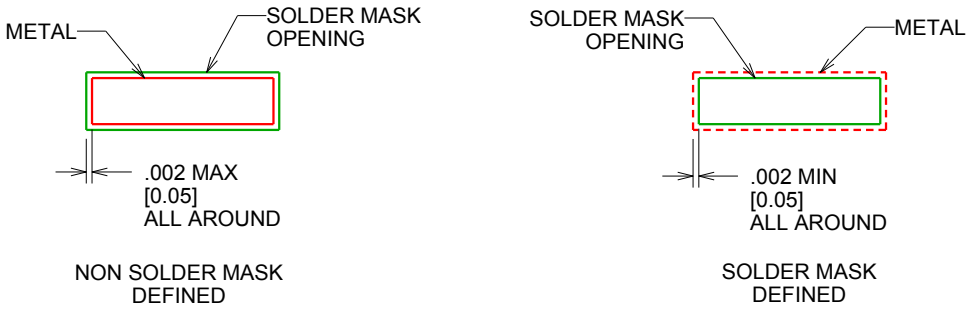


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MO-137, variation AB.



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

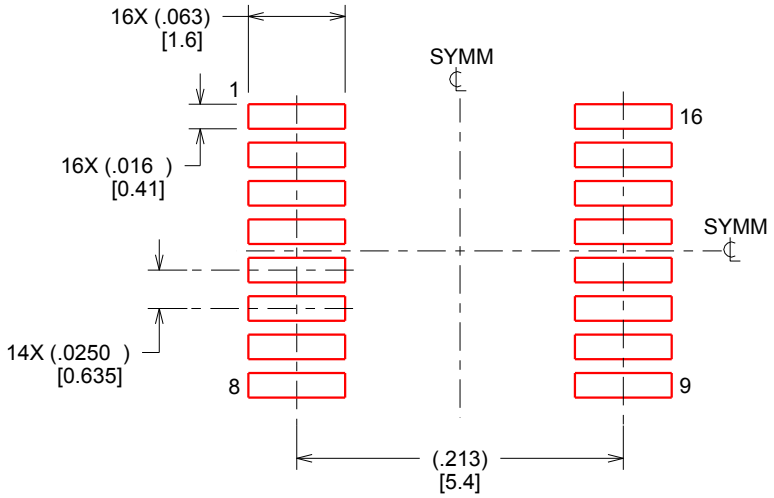
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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最后更新日期：2025 年 10 月